Towards realistic electronic structure calculations of strongly correlated electron system s

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We review some aspects of the realistic in plementation of the dynamical mean-eld method. We extend the techniques introduced in Ref. 1 to include the calculations of transport coecients. The approach is illustrated on La_{1 x} Sr_xT iO₃ material undergoing a density driven Mott transition.

I. IN TRODUCTION

In recent years understanding of the physics of strongly correlated m aterials has undergone trem endous increase. This is in part due to the advances in the theoretical treatm ents of correlations, such as the developm ent of dynamicalmean-eld theory $(DMFT)^1$. The great allure of DMFT is the exibility of the method and its adaptability to dierent systems as well as the simple conceptual picture it allows us to form of the dynam ics of the system. The mean-eld nature of the method and the fact that the solution maps onto an impurity model, many of which have been thoroughly studied in the past, means that a great body of previous work can be brought to bear on the solution of models of correlated lattice electrons. This is exemplified by the great m any num erical m ethods that can be employed to solve the DMFT equations.

DMFT has been very successful in understanding the mechanism of the M ott transition in model H am iltonians. We now understand that the various concentration induced phase transitions can be viewed as bifurcation of a single functional of the Weiss eld. The phase diagram of the one-band H ubbard model, demonstrating that there is a rst order M ott transition at nite temperatures is fully established ¹. Furtherm ore Landau like analysis demonstrates that all the qualitative features are quite generic at high temperatures ². However the lowtem perature ordered phases, and the quantitative aspects of the spectra of speci cm aterials clearly require realistic treatment.

This triggered realistic development of DMFT in the last decade which has now reached the stage that we can start tackling real materials from an almost ab initio approach^{3,4}, something which in the past have been exclusively in the domain of density functional theories. We are now starting to see the merger of DMFT and such ab initio techniques and consequently the opportunities for doing real electronic structure calculations for strongly correlated materials which so far were not within

the reach of traditional density functional theories.

Density functional theory (DFT)⁵ is canonical exam ple of ab initio approach, very successful in predicting ground state properties of many systems which are less correlated, for example the elemental metals and sem iconductors. However it fails in more correlated materials. It is unable to predict that any system s is a M ott insulator in the absence of magnetic order. It is also not able to describe correctly strongly correlated metallic state. As a matter of principle DFT is a theory of ground state or them odynam ic properties at nite tem peratures. It's Kohn-Sham spectra cannot be rigorously identied with the excitation spectra of the system. In weakly correlated substances the Kohn-Sham spectra is a good approximation to start a perturbative treatment of the one-electron spectra using the GW method⁶. However this approach breaks down in strongly correlated situations, because it is unable to produce H ubbard bands. In orbitally ordered situations the LDA+U method 7 produces the Hubbard bands, however this method fails to produce quasiparticle bands and hence it is unable to describe strongly correlated m etals. Furtherm ore, once long range order is lost the LDA+U method reduces to LDA and hence it becom es inappropriate even for M ott insulators.

Dynamical mean-eld theory is the simplest theory that is able to describe on the same footing total energies and the spectra of correlated electrons even when it contains both quasiparticle and Hubbard bands. Combined with LDA, one then has a theory which reduces to a successfulm ethod (LDA) in the weak correlations limit. In the static limit, one can show 8 that LDA+U can be viewed as a static limit of LDA+DMFT used in conjunction with the Hartree-Fock approximation. Therefore LDA+U is equivalent to LDA+DMFT+ further approximations which are the only justified in static ordered situations. Up to now, the realistic LDA band structure was considered with DMFT for purpose of computing one-electron (photoem ission) spectra and total energies.

Following Refs. 1,3,4 in this paper we extend this approach to computation of transport properties. Many

transport studies within DMFT applied to modelHamiltonians have been carried out, and the strengths (non-perturbative character) and limitations (absence of vertex corrections) are well understood. However applications to realmaterials require realistic computations of current matrix elements.

There are two ways in which DMFT can be used to understand the physics of real materials. The simplest approach, outlined in Ref. 1,3 is closely tied to the idea of model Ham iltonians. This requires i) methodology for deriving of the hopping parameters and the interaction constants ii) a technique for solving the dynamical mean-eld equations and iii) an algorithm for evaluating the transport function which enters in the equations of transport coe cients. The second direction is more ambitious and focus on an integration of i) and ii) using functional formulations⁹.

In this paper we review the rst approach. The emphasis here is in illustration of di erent aspects of the modeling which a ect the nalanswer. This is necessary to obtain a balanced approach towards materials calculations. There are now many impurity solvers, they dier in their accuracy and computational cost. In the present paper we use two impurity solvers the Hirsch-Fye Quantum Monte Carlo (QMC) method 10 and symmetrized nite-UNCA method (SUNCA) 11 comparing them in the context of sim pli ed m odels without the additional com plications of real materials. Instead we use the SUNCA m ethod as an impurity solver to compute the transport properties and new developments using La_{1 x}Sr_xTiO₃ as an example material 12. For other reviews of realistic implementations of DMFT and electronic structure see Ref. 13.

In the next section II we shortly review a basic dynam ical mean—eld theory concepts and their application to realistic structure calculations. As computation of transport parameters requires knowledge of the self-energy coming from DMFT calculations which is based on impurity solvers we present a short review of two impurity solvers used in the paper in section III. Theory of the transport calculations is given in section IV. Test system used for transport calculations, which is doped LaTiO $_3$ ceramics, and DMFT results are described in section V. Results of dc-transport calculations are presented in section VI. And nally we come to conclusion in homonymous section VII.

II. DYNAM ICAL MEAN FIELD THEORY

A. Realistic DM FT form alism

A central concept in electronic structure theory is the f-m odel H am iltonian. Conceptually, one starts from the fullm any body problem containing all electrons and then proceeds to elim inate some high-energy degrees of freedom. The results is a H am iltonian containing only a few bands. The determination of the model H am iltonian is a

di cult problem in itself, which has received a signi cant attention 14,15,16,17,18,19,20 . The K ohn-Sham H am iltonian is a good starting point for the kinetic part of the H am iltonian and can be conveniently expressed in a basis of linear mun-tin orbitals (LM TO's) 21 , which need not be orthogonal (see Appendix B)), as

$$H_{LDA} = ("_{im im ; jm \circ} + t_{im ; jm \circ}) c_{im}^{y} c_{jm \circ}; (1)$$

$$im ; im \circ;$$

where i; j are atom ic site indexes, m is orbital one, and denotes spin.

It is well known that LDA severely underestimates strong electron interactions between localized d- and f-electrons because the exchange interaction is taken into account only approximately via the functional of electron density. To correct this situation, the LDA Ham iltonian can be supplemented with a Coulomb interaction term between electrons in the localized orbitals (here we will call them a heavy set of orbitals). The largest contribution comes from the Coulomb repulsion between electrons on the same lattice site that we will approximate by the interaction matrix U $^{\rm i}$ of the heavy shell (h) of atom i as

$$H_{int} = \frac{1}{2} \sum_{im 2h}^{X} U_{m_{1}m_{2}m_{1}m_{2}}^{i} C_{im_{1}}^{y} C_{im_{1}}^{y} C_{im_{2}}^{y} C_{im_{2}}^{y} C_{im_{2}}^{0} C_{im_{1}}^{0} ;$$
(2)

where m are orbital and are spin indexes. In the diagonal density approximation electron { electron interaction matrix $U_{m_1m_2m_1^0m_2^0}^{i}$ can be represented using screened C oulomb and exchange vertexes as

$$U_{m m \circ} = \operatorname{lm} m \operatorname{^{0}} \mathcal{V}_{C} \operatorname{jm} m \operatorname{^{0}} \mathbf{i};$$

$$J_{m m \circ} = \operatorname{lm} m \operatorname{^{0}} \mathcal{V}_{C} \operatorname{jm} \operatorname{^{0}} m \mathbf{i};$$
(3)

which are expressed via Slater integrals $F^{(i)}$, i=0;2;4;6 in the standard manner 22 . The Slater integrals can be linked to the average intra{atom ic repulsion U and exchange J obtained from , e.g., LSDA supercellprocedures via $U=F^0$ and $J=(F^2+F^4)=14$. The ratio $F^2=F^4$ is to a good accuracy a constant 0:625 for d-electrons. Using the C oulomb and exchange matrices we can rewrite the interaction term as

$$H_{int} = \frac{1}{2} \sum_{i=0}^{X} U^{i} \circ n_{i} n_{i} \circ = \frac{1}{2} \sum_{i m m^{0}}^{X} U^{i}_{m m} \circ n_{im} n_{im} \circ + \frac{1}{2} \sum_{i m 6 m^{0}}^{X} (U^{i}_{m m} \circ J^{i}_{m m^{0}}) n_{im} n_{im} \circ ; \qquad (4)$$

where index = (m;) combines the orbital and spin indexes. This equation also provides de nition of the interaction matrix U $_{\circ}$ which will be used further in the paper.

The LDA Ham iltonian already contains a part of the local interaction which has to be subtracted to avoid the double counting. The full Ham iltonian is thus approximated by

$$H = H_{LDA} + H_{dc} + H_{int} = H^{0} + H_{int};$$
 (5)

where H 0 is the one-particle part of the H am iltonian and will play a role of the kinetic term within a DM FT approach. The double counting correction can not be rigorously derived within LDA+DM FT. Instead, it is commonly assumed to have a simple static H artree-Fock form, just shifting the energies of the heavy set

$$H_{dc m}$$
; $o_{m} \circ (k) = m$; $o_{m} \circ m \in E_{dc}$: (6)

Here, is atom ic index in the elementary unit cell. The $\sin p$ lest approximation $\cos m$ only used for E $_{dc}$ is 3,7

$$E_{dc} = U (n_h \frac{1}{2});$$
 (7)

In the spirit of DMFT, the self-energy is assumed to be local, i.e. k-independent, and non-zero only in the block of heavy orbitals. Therefore it is convenient to partition the Ham iltonian and the Green's function into the light and heavy set (denoted by land h, respectively) as

$$G (k;!) = (! +) \begin{pmatrix} O_{hh} & O_{hl} \\ O_{lh} & O_{ll} \\ O_{lh} & O_{ll} \end{pmatrix} (8)$$

$$H_{hh}^{0} & H_{hl}^{0} \\ H_{lh}^{0} & H_{ll}^{0} \\ \end{pmatrix} (8)$$

where [:::] means matrix inversion, is the chemical potential and 0 is the overlap matrix (see Appendix A).

Them ain postulate of the D ynam icalM ean-Field Theory (DMFT) 1 form alism is that the self-energy is local, i.e. it does not depend on momentum, (k;!) = (!). This postulate can be shown to be exact in the limit of in nite dimensions provided that the hopping parameters between dierent sites are scaled appropriately. Within this approach, the original lattice problem can be mapped onto an Anderson in purity model where the local Green's function and the self-energy, G $_{\rm loc}$ and , are identied with the corresponding functions for the impurity model, i.e.

$$_{im p}(!) = (!) \text{ and } G_{im p}(!) = G_{loc}(!)$$
: (9)

Equations (9) along with the trivial identity

$$G_{loc}(!) = X G_{k}(!);$$
 (10)

constitute a closed set of self-consistent equations. The only thing that rem aims is to solve the Anderson impurity model.

Notice that statem ent that the self-energy is diagonal is the basis dependent statem ent and if (i! $_{\rm n}$) is m om entum independent in one basis and U $_{\rm k}$ is a unitary transform ation from one basis to another, and LM TO H am iltonian, H $_{\rm LD\,A}$ in the new basis is given by U $_{\rm k}$ H $_{\rm LD\,A}$ U $_{\rm k}^{\rm y}$, then the self-energy in the new basis $^{\rm 0}$ = U $_{\rm k}$ (i! $_{\rm n}$)U $_{\rm k}^{\rm y}$ is m om entum dependent. Therefore DM FT approximation, if at all valid, is valid in one basis $^{\rm 23}$. Hence, we will

work in a very localized basis where the DMFT approximation is most justiled.

In DMFT we construct the self-energy, , as a solution of an Anderson impurity model with a non-interacting propagator (Weiss function) $G_{\rm 0}$

$$S_{\text{im p}} = \begin{array}{c} X \\ c^{+} ()G_{0} & ^{1}_{0} (; ^{0})c \cdot (^{0}) \end{array}$$

$$+ \begin{array}{c} X \\ U & ^{0} \\ ^{0}2 \text{ h} \end{array}$$
(11)

where and 0 are running over indexes m . The W eiss function can be linked to the lattice quantities through the local G reen's function and self-energy being are related to each other by the D yson equation

$$G_{loc}(i!_n)^{-1} = G_0(i!_n)^{-1}$$
 (i!_n): (12)

Combining Eq. (8), (10) and (12) we nally obtain

$$G_0^{1}(i!_n) = X \frac{1}{(i!_n + 0)_k H_k^0 (i!_n)} + (i!_n):$$
(13)

One can solve a very general impurity model de ned by the action (11) and Weiss eld (13). But it is much cheaper to elim inate the light (weakly interacting) bands and de ne an elective action in the subspace of heavy bands only. In this way, the local problem can be substantially simplied.

1. Downfolding

When a group of bands is well separated from the others it is clear that a reduced description of the problem is possible. In the one-electron approach it goes under the name downfolding 24 . There are several prescriptions to carry out this procedure in the context of DM FT . Perhaps, the simplest approach is to reduce the H am iltonian (H 0 + H $_{\rm int}$) (see Eqs. (2), (1)) to the one having H ubbard like form for the bands in question . To estimate the hopping elements one can perform a tight-binding t. The value of U to be used is then reduced, since ones computed in the constrained density functional calculations, it is screened by the bands which have been eliminated. A fler this procedure we arrive to a H ubbard H am iltonian with a small number of bands

all num ber of bands

$$X$$

 $H = t_{ij}^{m m} c_{im}^{y} c_{jm} + H_{int};$

where i; j run over lattice sites and m; m^0 (; 0) label the orbital (spin) indices of the heavy set of orbitals.

We can also perform the downfolding at the level of DMFT. The starting point is Eq. (8) which is used to get the heavy block G reen's function

$$G_{hh}(!) = {\begin{array}{*{20}{c}} X & h \\ & M_{hh}^{k} & M_{hl}^{k}M_{ll}^{k} & M_{lh}^{k} & & i_{1} \\ & & & & & \\ & & & & & \\ & & & & & \\ & & & & & \\ & & & & & \\ & & & & & \\ & & & & & \\ & & & & & \\ & & & & & \\ & & & & & \\ & & & & & \\ & & & & & \\ & & & & & \\ & & & & & \\ & & & & & \\ & & & & & \\ & & & & & \\ & & & & & \\ & & & & & \\ & & & & \\ & & & & \\ & & & & \\ & & & & \\ & & & & \\ & & & & \\ & & & & \\ & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & \\ & & & \\ & & \\ &$$

where the quantity M^{k} is dened as

$$M^{k} = (! +)0 (k) H^{0}(k);$$
 (15)

here is a double index which is combination of h and l.

The low-energy form of Eq. (14) can be found by expanding around zero frequency and to linear accuracy in! we obtain

$$G_{hh} (!) = \begin{array}{c} X & h & & i \\ & Z_k^{1}! & P (k) & & hh \end{array}; \quad (16)$$

where renormalization amplitude $Z_{\,k}$ and elective H amitonian are given by

$$Z_{k}^{1} = O_{hh} + K_{hl}K_{ll}^{1}O_{ll}K_{ll}^{1}K_{lh}$$

$$O_{hl}K_{ll}^{1}K_{lh} K_{hl}K_{ll}^{1}O_{lh};$$

$$P(k) = H_{hh}^{0} K_{hl}K_{ll}^{1}K_{lh};$$

$$K = H^{0} O : (17)$$

Further, we can choose a new base in the heavy block such that the local G reen's function has the usual form . First we de ne the average renormalization amplitude

$$Z = X Z_k ; \qquad (18)$$

and choose the transform ation matrix such that

$$S^{Y}Z^{1}S = 1$$
: (19)

The new overlap matrix and e ective Hamiltonian become

$$O_{eff}(k) = S^{y}Z_{k}^{1}S; \qquad (20)$$

$$H_{eff}(k) = S^{\gamma} \mathbb{F}(k) S + O_{eff}(k);$$
 (21)

$$= S^{y}_{hh}S; (22)$$

and $% \left(1\right) =\left(1\right) +\left(1\right) =\left(1\right) +\left(1\right) +\left(1\right) =\left(1\right) +\left(1\right)$

$$G_{hh} = {\overset{X}{[(! +)O_{eff}(k) \ H_{eff}(k) \]}}^{1};$$
 (23)

with the Dyson equation

$$G_{hh}^{1} = G_{0hh}^{1}$$
 ; (24)

and corresponding W eiss function de ned as

$$G_{0hh} = [(! +)]^{-1};$$
 (25)

where hybridization function regularly behaves at innity.

The self-energy of the reduced model (23) is local, therefore the DMFT treatment is applicable. In this case, only the heavy bands need to be considered in calculation which greatly simplies the complexity of the problem.

The reduced model, however, has in general more complicated Coulomb interaction matrix than we chose in

the originalm odel. If we assume, that the diagonal components of Z are much larger than the o-diagonal, we obtain the same $\sin p \ln H$ ubbard-type interaction term within reduced model for the heavy block. The Coulomb interaction is however screened by the light bands and is reduced to

We can estimate the magnitude of the reduction of Coulomb repulsion by evaluating the above quantity explicitly. In the case the original base is orthogonal, i.e. O = 1, we get

$$\frac{U}{U} = \frac{1}{N} \text{Tr H}_{h1}^{0} = \frac{1}{H_{11}^{0}} = \frac{1}{H_{1h}^{0}}; \quad (27)$$

where N is the number of heavy bands.

In the case when the reduced model corresponding to Eq. (23) is degenerate and the basis is orthogonal (the overlap matrix $O_{\rm eff}$ (k) is equal to unity) the self-energy and local Green's function are also degenerate and diagonal. Then the momentum sum in Eq. (23) can be replaced by the integral over energy and the local Green's function can be calculated using the standard Hilbert transform ation

$$G(i!_n) = \begin{bmatrix} Z_{+1} \\ i!_n + (i!_n) \end{bmatrix}$$
(28)

Here, the density of states D (") is the density of states of the kinetic part of the reduced model $H_{eff}(k)$ in Eq. (23).

O ther groups have used for D (") rescaled partial D O S as discussed in Appendix B . Possibility to use the H ilbert transform ation is substantially simplies the calculation procedure and brings a number of conceptual simplications $^{\rm 13}$.

2. Upfolding

Upfolding is a procedure which is \inverse" to the downfolding one. One needs to use Eq. (22) to transform the self-energy obtained from DMFT calculations, , to the one, $_{\rm hh}$, which is inserted to the original LDA H am iltonian in order to compute the local G reen's function (GF) G (i! $_{\rm n}$). The local GF with upfolded self-energy reads

$$G (i!_{n}) = \begin{array}{c} Z \\ G (i!_{n}) = \begin{array}{c} dk & (i!_{n} + &) & \begin{array}{c} O_{hh} & O_{h1} \\ O_{lh} & O_{ll} \end{array} & (29) \\ & & & & \\ H_{hh} & H_{h1} & & hh & H_{dc} & 0 \\ H_{lh} & H_{ll} & & & & \\ \end{array} ,$$

where is the LDA chem ical potential and H $_{\rm dc}$ is the double counting term Eq. (6). Instead of using form ula (7), we rather deduce the constant shift of the heavy set

ofbands by equating the total number of electrons to the integral of the spectral function

$$A(!) = \frac{1}{m} \text{Im} \quad G(k;!) O^{k};$$

multiplied by the Ferm i function.

3. Algorithm to solve DMFT equations

To close the set of DMFT equations, a m ethod to solve the local problem is required. In the following, we will focus our attention on two impurity solvers: QMC and SUNCA. In section III, we will brie y review both m ethods while a detailed comparison between the results obtained by those two approaches is given in section VD. Bellow, we summarize basic steps in the DMFT self-consistent scheme that delivers the local self-energy—crucial quantity to calculate transport and optical properties of a solid.

W e started the iteration by a guess for the W eiss eld G_0^{-1} from which the local G reen's function $G_{\rm loc}$ was calculated by one of the impurity solvers. The self-energy was then obtained by the use of the Dyson equation (24). Mom entum sum mation over the Brillouin zone, Eq. (23), delivers a new guess for the local G reen's function and through the Dyson equation also for the Weiss eld G_0^{-1} . The iteration is continued until the convergence is found to the desired level. The scheme can be illustrated by the following ow-chart

$$G_0^{-1}$$
 IM P solver G DE DM FT SCC G_0^{-1} ;

where $\DE"$ stands for the Dyson equation (24) and \DMFT SCC" means the DMFT self-consistent condition Eq. (23) or (28).

The QMC impurity solver is dened in imaginary time, therefore the following additional Fourier transform ations between imaginary time and Matsubara frequency points are necessary

$$G_0$$
 (i!) $^{\mathbb{F}_!^T}G_0$ () $^{\mathbb{Q}M}_!^{\mathbb{C}}G$ () $^{\mathbb{F}_!^T}G$ (i!):

Here FT and IFT are Fourier and inverse Fourier transform ations, respectively. After the self-consistency is reached, the analytic continuation is required to obtain the real-frequency self-energy. This issue is addressed in section IIIC.

The SUNCA m ethod is in plemented on real frequency axis to avoid the ill-posed problem of analytic continuation. As an input, it requires the bath spectral function $A_c(!) = \frac{1}{2} \operatorname{Im} G_0^{-1}(!)$ and delivers the local spectral function $A_d(!) = \frac{1}{2} \operatorname{Im} G(!)$

The realpart of the local G reen's function is obtained by the use of the K ram ers-K ronig relation (KK).

III. IM PURITY SOLVERS

A m ong m any m ethods used to solve the im purity problem we chose the Q uantum M onte C arlo m ethod 10 and sym m etrized nite-U NCA m ethod 11 . In this section we brie y describe both of them .

A. The Quantum M onte Carlo m ethod

There are well known advantages and disadvantages of the QMC method and our choice is spurred by the fact that despite being slower than other methods the QMC is well controlled, exact method. As an input the QMC procedure gets Weiss function G_0 () and as an output it produces Green's function G (). We remind reader major steps taken for the QMC procedure. Usually one starts with impurity elective action S

where fc; c^{\dagger} g operators are ferm ionic annihilation and creation operators of the lattice problem, = fm; g.

The rst what we should do with the action (31) is to discretize it in imaginary time space with time step such that = L, and L is the number of time intervals

The next step is to get rid of the interaction term U by substituting it by sum mation over Ising-like auxiliary elds. The decoupling procedure is called the Hubbard-Stratonovich transformation^{25,26}

expf fU on no
$$\frac{1}{2}$$
 (n + no)gg = (32)

$$\frac{1}{2} X = \exp f \quad \circ S \quad \circ \text{ (n } \quad n \circ)g;$$

where $\cosh = \exp(\frac{U_0}{2})$, S o(1) are auxiliary Ising elds at each time slice.

In the one-band Anderson impurity model we have only one auxiliary Ising eld S ($_{\rm 1})=1$ at each time slice, whereas in the multiorbital case number of auxiliary elds is equal to number of ; $^{\rm 0}$ pairs, i.e. C $_{\rm 2}$. Applying the H ubbard-Stratonovich transform ation at each time slice we bring the action to the quadratic form with the partition function

$$Z = T r_{fS}$$
 $_{0()g}$ $detG$ $_{fS}$ $_{0()g}$; (33)

where GF in terms of auxiliary elds G 1 reads as

$$G_{:fS_{-0}g}^{1}(;^{0}) = G_{0}^{1}(;^{0})e^{V}$$
 (e^{V} 1) ; 0; (34)

with interaction matrix

$$V = \begin{matrix} X \\ \circ (6) \end{matrix}$$

w here

$$0 = +1 \text{ for } < 0$$

 $0 = 1 \text{ for } > 0$

Once the quadratic form is obtained one can apply W ick's theorem at each time slice and make the Gaussian integration by Grassmann variables to get the full interacting GF

G (; 0) =
$$\frac{1}{Z} T r_{fS \ og}$$
 (36)
G; fS og (; 0) $Y \det G^{1}_{0;fS \ og}$:

To evaluate sum m ation Eq. (36) one uses M onte Carlo stochastic sampling. The product of determ inants is interpreted as the stochastic weight and auxiliary spin congurations are generated by a M arkov process with probability proportional to their statistical weight. M ore rigorous derivation can be not elsewhere 1 , 26 .

Since the QMC method produces results in complex time (G ($_{\rm m}$) with $_{\rm m}$ = m , m = 1::L) and the DMFT self-consistency equations make use of the frequency dependent G reen's functions and self-energies we must have an accurate method to compute Fourier transforms from the time to frequency domain. This is done by representing the functions in the time domain by a cubic splined functions which should go through original points with condition of continuous second derivatives imposed. Once we know cubic spline coe cients we can compute the Fourier transform ation of the splined functions analytically (see Appendices C and D).

B. The SUNCA

In this section we brie y review the second method, used to solve the multiorbital Anderson impurity model, called Symmetrized nite-U NCA method 11. The method is based on the self-consistent perturbation theory with respect to the hybridization strength between the elective bath and the local system and is therefore exact in the atom ic limit. However, this method sums up an in nite class of skeleton diagrams and takes into account a subclass of singular vertex corrections that are necessary to obtain the correct dynamic lowenergy Fermi-liquid scale 11 and correct position of the Abrikosov-Suhl resonance. The SUNCA approximation does not contain only non-crossing diagrams but rather all the three-point vertex corrections of ladder-type and

should not be confused with the usual nite-U non-crossing approximation.

The SUNCA approach presents the advantage to provide directly real frequencies one-particle G reen's functions. Local quantities like densities of states can therefore be computed for any regime of parameters without having to perform analytical continuation. Furthermore, the SUNCA method can be applied to arbitrary multiband degenerate Anderson in purity model with no additional numerical cost. This is an important advantage compared to some other methods like Quantum Monte Carbo or exact diagonalization. The method is especially relevant for systems with large orbital degeneracy such as systems with f-electrons.

The pathologies that severely lim it the usefulness of the non-crossing approximation in the context of DMFT are greatly reduced with inclusion of ladder-type vertex corrections. Nevertheless, they do not completely rem ove the spurious peak that form s at tem peratures substantially below the Kondo temperature. To overcome this shortcoming, we employed an approximate scheme to smoothly continue the solution down to zero temperature. This was possible because at the break-down tem perature the solution of SUNCA equations shows an onset of the Ferm i-liquid state. As we will show in the subsequent chapters by comparison with QMC, SUNCA gives correct quasiparticle renormalization amplitude Z and the real part of the self-energy at zero frequency approaches the Luttinger value. The im aginary part of the self-energy, however, has a narrow spurious deep on top of the parabola that is form ed around zero frequency. To rem ove the deep, we matched the Ferm i-liquid parabolic form for imaginary part of the self-energy in the smallwindow of the deep such that it smoothly connected the interm ediate frequency region where the parabola was form ed. W e num erically found that this SUNCA pathology is rapidly reduced with increasing the number of bands i.e. it is much less severe in the case of three-band m odel than in one-band case.

Next, we give some details of the auxiliary particle technique together with the de nition of the SUNCA approximation. Within the auxiliary diagrammatic method, the local degrees of freedom can be represented by auxiliary particles. To each eigenstate of the local Hamiltonian H $_{loc}$ ji = E_n ji we assign an auxiliary operator a_n such that ji = a_n^y jvaci. A general Anderson impurity model can then be expressed by

where $F_{n,n^0}^m = \text{Im } j d_m^y \ j n^0 i$, d_m^y is a creation operator for the local electron and c_{km}^y creates an electron in the bath and m stands for the spin and band index. In order that electrons are faithfully represented by the auxiliary particles, two conditions must be satis ed:

(i) An auxiliary particle a_n must be boson (ferm ion) if the state \dot{n} i contains even (odd) number of electrons.

(ii) The local charge Q $n = n a_n^y a_n$ m ust be equal to one at all times Q = 1 expressing the completeness relation for the local states n = n n = 1.

The rst condition merely request some care that has to be taken in evaluating diagrams while the second constraint, projection onto the physical Hilbert space, is somewhat more involved but can still be done exactly. The term Q can be added to the Hamiltonian and the limit! 1 has to be taken after the analytic continuation to the real frequency axes is performed. Taking this limit, actually leads to a substantial simplication of the analytic continuation. Namely, when evaluating self-energies for the pseudo-particles, only the integrals around the branch-cuts of the bath electron Green's function have to be considered while the integrals around the auxiliary particle Green's functions vanish by the projection.

The physical local G reen's function (electron G reen's function in Q=1 subspace) can eventually be calculated with the help of the Abrikosov trick²⁷ which states that the average of any local operator that vanishes in the Q=0 subspace is proportional to the grand-canonical (all Q values allowed) average of the same operator

$$hA i_{Q=1} = \lim_{\substack{! \ 1}} \frac{hA i_{G}}{hO i_{G}}$$
: (38)

By realizing that the local G reen's function is proportional to the bath electron T-m atrix, we have

$$G_{loc} = \lim_{! \ 1} \frac{1}{V^2 h0 i_c}$$
 c; (39)

where $_{\rm c}$ is the bath electron self-energy calculated in the grand-canonical ensemble.

In the case of degenerate Anderson in purity model, an important simplication occurs in the Ham iltonian Eq. (37). Namely, pseudo-particles, corresponding to the states with the same number of electrons on the impurity site, are degenerate with energies $E_{\rm M}=M+UM$ (M 1)=2, and pseudo G reen's functions

$$G_{M}$$
 (i!) = 1=(i! E_{M} M (i!)); (40)

where M is the number of electrons on the impurity. In the case of Anderson impurity model with N=2 bands, we need to consider only N+1 dierent propagators instead of dealing with $2^{\rm N}$ pseudo-particles. Furthermore, if U is large and we are interested in doping levels not too far from an integer lling with M electrons, i.e. close to the Mott-insulating state, it is reasonable to assume that only uctuations between local states with M 1, M and M+1 electrons on the impurity need to be considered. The single particle spectra will thus consist of lower Hubbard band, upper Hubbard band and a quasiparticle resonance while we ignore other Hubbard bands that are even more far away from the chemical potential.

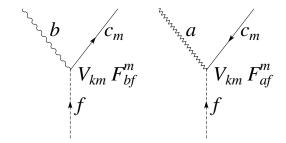


FIG. 1: The two bare vertices considered in the case of degenerate Anderson impurity model. Throughout this paper, conduction-electron c propagator is represented by solid line, while wiggly, dashed and zigzag lines correspond to the pseudo-particles with M $\,$ 1, M and M + 1 electrons on the impurity, respectively.

For example, in the case the lling is less than 1:5 we take into account empty state, singly occupied and doubly occupied states on the impurity while the triple occupancy is neglected. This is equivalent to adding to the original Hamiltonian an in nite three-particle interaction.

In the following, we will use letter b to denote the auxiliary particles with M 1 electrons on the impurity, f for M and a for M + 1 electrons on the local level, respectively. In Fig. 1 we show the two bare three-point vertices that are left to us in the case of degenerate Anderson impurity model when considering those three types of states. Note that pseudo-particle b is $\frac{N}{M}$ de-

generated, f is $\frac{N}{M}$ and a is $\frac{N}{M+1}$ degenerated, respectively. In case M is odd (even), particles a and b are bosons (ferm ions) while f are ferm ions (bosons).

The SUNCA approximation is a conserving approximation de ned by a Luttinger-W and type functional from which all self-energies are obtained as a functional derivatives, $_{a}=\frac{1}{G_{a}}$. The building blocks of are dressed Green's functions of pseudo-particles G_{b} (depicted as a wiggly line), G_{f} (dashed line), G_{a} (zigzag line) and bath electron G_{c} (solid line). Due to the exact projection, only pseudo-particles are fully dressed while bath electron Green's function is not dressed.

The choice of diagrams was motivated by the Schrie er-W olf transform ation showing that both uctuations from M to M 1 and M to M+1 have to be considered totally sym m etrically. In the case of one-band m odelwe have for the exchange coupling $J = J_1 + J_2 =$ $V^{2}(\frac{1}{1}+\frac{1}{11})$. The exact K ondo tem perature is proportional to $\exp(=J) = \exp(=(J_1 + J_2))$. It is well known that if one takes into account only non-crossing diagram s, the K ondo scale of the resulting approxim ation steeply drops with decreasing U and is of the order =J2) which can be orders of magnitude of exp $(=J_1)$ w rong. This happens because the simultaneous uctuations between all three types of pseudo-particles are neglected. As was shown in Ref. 11, one needs to sum up an

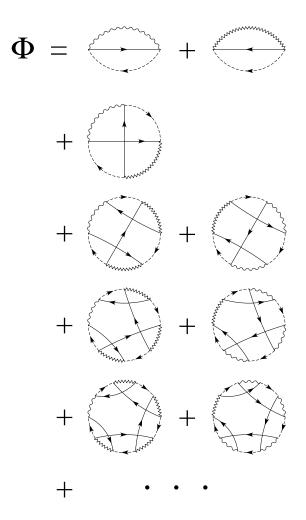


FIG. 2: D iagram m atic representation of the SUNCA generating functional to describe the degenerate Anderson impurity model.

in nite number of skeleton diagrams (SUNCA diagrams) to recover the correct exchange coupling consisting of two terms J_1 and J_2 , generated from the two types of vertices depicted in Fig. 1.

The SUNCA Luttinger-W ard functional, shown in Fig. 2, consists, in addition to NCA contributions (rst two diagrams), of the diagrams where two conduction electron lines cross only ones and the rest of the electron lines cross twice. Diagrams not included in SUNCA have higher order crossings. The lowest order neglected are of CTMA-type^{28,29} where all conduction electrons cross exactly twice. Note that due to the projection, any contribution to the Luttinger-W ard functional consists of a single ring of pseudo-particles since at any moment in time there must be exactly one pseudo-particle in the system.

The SUNCA self-energies, obtained by di erentiating the Luttinger-W and functional, are shown in Fig. 3. The part of the pseudo-particle ring, where conduction electrons cross exactly twice, can be rewritten in the ladder type T-m atrix. The additional two conduction lines, that

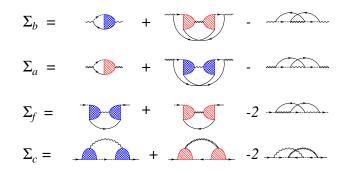


FIG. 3: Diagram matic representation of the self-energies, derived from SUNCA Luttinger-W and functional (Fig. 4) in terms of the renormalized hybridization vertices, de ned in Fig. 4. In each line the third diagram is subtracted in order to avoid double counting of terms within the 1st two diagrams.

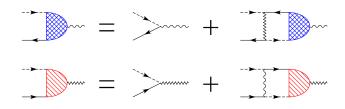


FIG. 4: D lagram m atic representation of the Bethe-Salpeter equations for ladder-type three-point vertex function.

cross only once, enable us to close T-m atrix and convert it into three-point vertex shown in Fig. 4. This is im-portant from practical point of view since the tree-point vertex is num erically much more tractable than the full four-point vertex.

The expressions for the self-energies de ned by Fig. 3 and Fig. 4, together with the de nitions of the Green's functions, Eq. (40), constitute a set of non-linear integral equations for ; = a;b;f. The local Green's function is calculated from the Eq. (39) using the self-consistently determined auxiliary propagators G. The SUNCA equations are given explicitly in Appendix E.

The SUNCA equations have been evaluated numerically by iteration. The two self-consistent loops, SUNCA and DMFT, can be merged together into one single set of equations. Starting with the initial guess for the bath spectral function $A_{\rm C}$ and pseudo-particle G reen's functions G , the rst guess to the T-matrix de ned in Fig. 4 is determined. With this, the pseudo-particle self-energies as well as the local G reen's function may be deduced. From the DMFT self-consistent condition, the new bath spectral-function is calculated. With the updated pseudo-particle G reen's functions and the new bath spectral-function one determines next approximation for the T-matrix, pseudo-particle self-energies and local G reen's function. The iteration is continued, until the convergence is found to the desired level.

C. A nalytic continuation of the self-energy

The QMC simulation produces Green's function G () of imaginary time = it or equivalently Green's function and the self-energy de ned in M atsubara frequency points. However, real-frequency self-energy is needed to obtain transport quantities. The analytic continuation of QMC data is required, which is an ill-posed problem and altogether hopeless if the precision of data is not extrem ely good and if the statistical errors are not taken into account properly. As is well known, Pade method is not very useful for analytic continuation of noisy QMC data. The maximum entropy method (MEM)30 tries to overcome this problem by adding an entropy term to the functional to be m in im ized. This is one of the best m ethods present available and usually produces real-frequency G reen's function of relatively high quality provided the data are carefully analyzed. We refer the reader to the original literature for the details 30 .

However, the quasiparticle peak for realistic density of states can have quite reach structure since at low tem perature it tries to reproduce the LDA bands around the Ferm i-level, i.e., the spectral function approaches the LDA density of states contracted for the quasiparticle renormalization amplitude Z, A(!) = (! = Z + 0). The maximum entropy method has a tendency to smear out this reach structure because of the entropy term . At low tem perature, this can lead to overshooting of spectral function and subsequently to the non-physical self-energy that ruins the causality. To avoid this pathology, we som etim es found useful to directly decom pose the singularkemelwith the Singular Value Decom position (SVD). W hen constructing the real frequency data, we took into account only those singular values, which are larger than precision of the QMC data.

Im aginary time G reen's G () can be expressed by the spectral function as

$$Z$$
 $G() = d! f(!) e^{!} A(!);$ (41)

or in discretized form

$$G = \begin{matrix} X \\ f(!)e & !A_! \\ ! \end{matrix} = \begin{matrix} X \\ V_m S_m U_{m!}A_!; \\ (42) \end{matrix}$$

where $UU^y = 1$ and $V^yV = 1$ are orthogonal matrices and S is diagonal matrix of singular values. The inversion is than $\sin p \ln y$ given by

$$A_{!} = {X \atop m} U_{m !} \frac{1}{S_{m}} V_{m} G : \qquad (43)$$

The magnitude of singular values drops very fast and only rst few terms in the upper sum can be determined from the QMC data. The rest of the information, that determines mostly higher frequency points, can be acquired from the SUNCA spectral function. We therefore

approximated the sum in Eq. (43) by

where M $\,$ can be determ ined by the precision of the Q M C data, i.e., $\,$ V $_{\rm M}$ $\,$ G $\,$ > S $_{\rm M}$.

We plot the sum (44) in Fig. 5 where rst 3, 6 or 9 coe cients were obtained from the QMC data. The corresponding smallest singular value is printed in the legend of the same gure. For comparison, we also display the spectral function obtained by the maximum entropy method and the SUNCA solution for the same parameters. The dierence between the various curves gives as a rough estimate for the accuracy of the technique. As we see, the quasiparticle resonance is obtained by reasonably high accuracy, while the Hubbard band is determined with less accuracy. In the inset of Fig. 5 we plot the same curves in a broader window. As we see, the SVD does not guarantee the spectra to be positive at higher frequencies. This how ever does not prevent us to accurately determine most of the physical quantities.

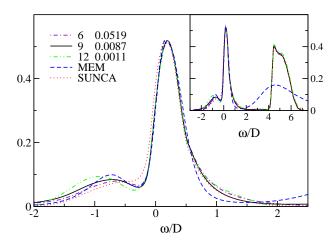


FIG.5: Spectral function for sem icircular D O S, inverse temperature = 16 and density n = 0.8. D ot-dashed, full and double-dot-dashed curve correspond to the sum (44) with M chosen to be 6, 9 and 12, respectively. In legend, we also print the lowest singular value taken into account (S $_{\rm M}$). For comparison we show maximum entropy spectra (dashed curve) and SUNCA spectra (dotted line). The inset shows the same spectra in a broader window.

W ithin DMFT, the real frequency self-energy can be obtained from the localG reen's function by the inversion of the Hilbert transform. A Ithough the implementation is very straightforward, we will brie y mention the algorithm we used. In the high-frequency regime, we can expand the Hilbert transform in terms of moments of the

DOS as

$$w(z) = \frac{z}{z} \frac{D(")d}{z} = \frac{x}{z} \frac{h^{m}i}{z^{m+1}}:$$
(45)

The series can be inverted and solved for z

$$z(w) = \frac{1}{w} + h''i + (h''^2i h''i^2)w$$
$$+ (h''^3i 3h''^2ih''i + 2h''i^3)w^2 + \dots : (46)$$

For most of the frequency points, the expansion up to som e higher power (w8) gives already an accurate estim ation for the inverse function. However, when w gets large, we need to use one of the standard root-nding m ethods to accurately determ ine the solution. This is however much easier than general root-nding in complex plane since we always have a good starting guess for the solution. We start evaluating the inverse function at high frequency where the absolute value of G is small and we can use the expansion in Eq. (46). Then we use the fact that G reen's function is a continuous function of a real frequency and we can follow the solution from frequency point to frequency point by im proving it with few steps of a secant (or Newton) method. A special attention, however, must be paid not to cross the branch-cut and get lost in the non-physical complex plane. Therefore, each secant or Newton step has to be shortened if necessary. The self-energy is nally expressed by the inverse of Hilbert transform w 1 as

$$= ! + w^{-1}(G):$$
 (47)

Fig. 6 shows the imaginary part of self-energy obtained by both analytic-continuation methods. As a reference and comparison we also show the results obtained by SUNCA method, which is dened and evaluated on real frequency axes and hence does not require analytic continuation. The low-frequency part of the self-energy is again very reliably determined and does not dier for more than 3%.

IV. TRANSPORT COMPUTATION

A. Transport theory

The transport param eters of the system are expressed in terms of so called kinetic coecients, denoted here by $A_{\,m}$. The equation for the electrical resistivity, , is given by

$$=\frac{k_B T}{e^2} \frac{1}{A_0}; \tag{48}$$

and the therm opower, S, and the therm alconductivity, , are expressed through

$$S = \frac{k_B}{\dot{p}\dot{q}}\frac{A_1}{A_0};$$
 $= k_B A_2 \frac{A_1^2}{A_0}$: (49)

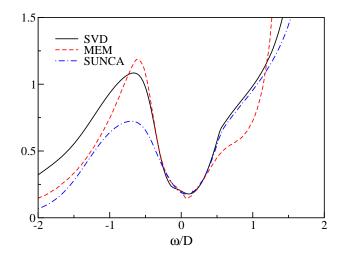


FIG. 6: Im aginary part of the self-energy obtained from the G reen's function by the inverse of the H ilbert transform . Full-line was obtained by the Singular Value decomposition, dashed by the maximum entropy method and dot-dashed by SUNCA. Parameters used are the same as in Fig. 5

W ithin the K ubo form alism 31 the kinetic coe cients are given in term sofequilibrium state current-current correlation functions of the particle and the heat currents in the system . Namely we have

$$A_{m} = {}^{m} \lim_{! \ ! \ 0} Z_{m} \ (i \ ! \ ! + i0) ;$$
 (50)

where

$$Z_0$$
 (i) = $\frac{ih}{i} \sum_{Z_0}^{Z} d \dot{e} hT \dot{f}^x () \dot{f}^x (0) i;$ (51)

$$Z_1(i) = \frac{ih}{i} Z^0 d e^i hT j^x()Q^x(0)i;$$
 (52)

$$Z_{2}(i) = \frac{ih}{i} \int_{0}^{2} de^{i} h T Q^{x}(0)q^{x}(0)i$$
: (53)

To evaluate these correlation functions, an expression for electric and heat currents, j^x and Q^x , are needed. Once those currents are evaluated, then calculation of the transport properties within DMFT reduces to the evaluation of the transport function

$$^{xx}() = \frac{1}{V_C} X_{k} Trfv_{k}^{x}()_{k}()_{k}()_{k}^{x}()_{k}()_{g};$$
 (54)

and the transport coe cients

$$A_{m} = N_{spin} h d^{xx}()f()f()'';$$
 (55)

The momentum integral in Eq. (54) extends over the Brillouin zone, V_C is the volume of the unit cell. The simplest form of the velocity is hk $\frac{1}{m} r_x k$ $i=v_k$ and it requires evaluation of matrix elements of r_x . However an alternative form of the current and the transport

function can be derived via the P eirls substitution generally in the non-orthogonal basis and is described in Appendix F. These two procedures generally give dierent answers 23,32,33 .

Next we de ne the energy dependent velocity as

$$\nabla_k () = \nabla_k \quad \nabla_k :$$
 (56)

The second term is due to the non-orthogonality of the basis or m ore speci cally due to overlap between orbitals at dierent sites, local non-orthogonality does not contribute to the velocity. The spectral density matrix $_{\rm k}$ () is the multiorbital generalization of the regular single orbital density of states and is given in terms of the retarded G reen's function, G , of the system by the equation

$$_{k}() = \frac{1}{2} G_{k}() G_{k}()^{*} :$$
 (57)

Finally the Green's function is given by

$$G_k(z) = (z +)O_k H_k^0(z)^{-1}$$
: (58)

Note here, that in accordance with the DMFT the self-energy matrix is assumed momentum independent. Now given an elective Ham iltonian for the system, an overlap matrix and the self-energy, the equations above give a complete prescription for computing the transport parameters. For computation of Eq. (54) we have developed two methods, one method generalizes the analytical tetrahedron method (ATM) 34 and the other one uses one-particle GF method in DMFT 3 , used to compute spectral densities in band structure calculations. First the total Hamiltonian, Hk () = Hk + () is diagonalized and written in the form

$$H_{k}() = O_{k}A_{k}^{R}()E_{k}()A_{k}^{L}()O_{k};$$
 (59)

where E_k is the diagonal matrix of complex eigenvalues and A_k^R and A_k^L are the right and the left eigenvector matrices respectively. Then the Green's function can be written as

$$G_{k}() = A_{k}^{R}()[(+)I E_{k}()]^{1}A_{k}^{L}();$$
 (60)

 $\mbox{\ensuremath{\mbox{w}}}$ ith I being the identity $\mbox{\ensuremath{\mbox{m}}}$ atrix. The transport function can now be expressed as

$$\begin{array}{rcl}
xx () & = & \frac{1}{2} \sum_{k,pq}^{X} Re & r_{k,pq}^{x} r_{k,pq}^{x} r_{k,pq}^{x} D_{k,p} D_{k,q} \\
& \frac{1}{2} S_{k,qp}^{x} t_{k,pq}^{x} + S_{k,pq}^{x} t_{k,qp}^{x} D_{k,p} D_{k,p} (D_{k,q}) & (61)
\end{array}$$

where the matrices r^x , s^x and t^x are

and D $_k$ is a diagonal m atrix de ned by

$$D_k = D_k()$$
 [(+)I $E_k()$]¹: (63)

When the computation of the transport function is carried out one is faced with computing integrals of the form

$$\begin{array}{c}
X & r_{k,pq}^{x} r_{k,qp}^{x} \\
 \hline
(+ E_{k,p}) (+ E_{k,q}); \\
X & s_{k,pq}^{x} t_{k,qp}^{x} \\
 \hline
(+ E_{k,p}) (+ E_{k,q});
\end{array} (64)$$

The strategy that is used to compute these integrals is sim ilar in spirit to the analytical tetrahedron method. The Brillouin zone is split up into a collection of equal sized tetrahedra and the integral over each tetrahedron is taken using linear interpolation between the four corners of the tetrahedron. In the analytical tetrahedron m ethod the num erator and the energy eigenvalues in the denom inator are linearized independently and the resulting integral is then done analytically. In our case we would want to follow the same rule which results in two linear functions in the denominator. Unfortunately we have not been able to evaluate that integral in the most general case, i.e. when none of the tetrahedron comers are degenerate although solutions can be found for degenerate cases when at least two of the four corners of the tetrahedron are identical. Hence we have to pursue further approximations which we outline below.

The two main integrals that we need to com pute are of the form

$$T_{SS}^{pq} = X \qquad F(k) (z = E_{k,p})(z = E_{k,q});$$

$$T_{OS}^{pq} = X \qquad F(k) (z = E_{k,p})(z = E_{k,q}) :$$

$$(65)$$

Here denotes the tetrahedron and SS indicates that the imaginary parts of both denom inators have the same sign and OS indicates that they have the opposite sign. This is ensured by the fact that the self-energy is retarded and z is real. For the diagonal case (p = q) the $T_{\rm SS}$ integral can be computed exactly by linearizing the eigenvalues in the denom inator, one simply needs to differentiate the ATM formulas by Lambin and V igneron 34 . For the diagonal $T_{\rm OS}$ however we note that the numerator is real and therefore we can write the integral in the following form

$$T_{OS}^{pp} = Im \begin{pmatrix} X & F(k) \\ k_2 & k_{pp} \end{pmatrix} \frac{1}{z E_{kpp}};$$
 (66)

where $_{k,p}$ = Im E $_{k,p}$. We note that $_{k,p}$ is solely due to the self-energy, which is momentum independent and thus it is reasonable to expect that $_{k,p}$ changes little with momentum. Hence the term in the parenthesis will be approximated linearly within the tetrahedron and the resulting integral can be computed with the ATM .

The o -diagonal case (p $\mbox{\it f}$ q) for both T_{SS} and T_{OS} is treated the same way so we will just look at T_{SS} . Both

factors in the denom inator are inspected and we determ ine which one has larger m odulus (on average if necessary). Then we write the integral on the form

$$T_{SS}^{pq} \dot{j}_{eq} = \frac{X}{(z E_k)_L} \frac{F(k)}{(z E_k)_L} \frac{1}{(z E_k)_S}; \quad (67)$$

where L indicates the denom inator with the larger m odulus and S indicates the one with the smaller modulus. The term in the parenthesis is now approximated linearly within the tetrahedron and the resulting integral can be computed with the ATM .

The approach described here to compute the transport function has been tested numerically against models where other methods can be used to evaluate the transport function. For cubic systems with nearest neighbor hopping one can for instance evaluate both the density of states and the transport function quite e ciently using Fast Fourier Transforms \mathbf{s}^1 . In general the results are quite accurate.

B. Small scattering lim it

In order to m ake connections with previous approaches to the computation of transport properties it is interesting to consider the small scattering limit. So we take the self-energy of the form

$$() = {}^{0}() + {}^{0}();$$
 (68)

where ⁰() is the real part of the self-energy m atrix, ⁰() is the imaginary part and is a small parameter. It is clear that the transport function will diverge as 1= and thus we can approximate the numerator matrix elements to zeroth order in . Within this approximation the transport function can be written as

$$^{\text{XX}}() = \frac{1}{V_{\text{C}}} {}^{\text{X}}_{k,p} (v_{k,p}^{\text{X}})^2 {}_{k,p} () (+ \frac{\rho}{K_{pp}});$$
 (69)

where $E_{k,p}^{\ 0}$ are the eigenvalues of $H_k^{\ 0}+0$ () and $V_{k,p}^{\ 0}$ denotes the corresponding band velocity. The lifetime $V_{k,p}$ () is form ally given by

$$_{k,p}\left(\right) =\frac{1}{2\,\,\,\lim_{k,p}j};\qquad \qquad (70)$$

here E $_{\rm k,p}$ are the eigenvalues of the fullH am iltonian. The im aginary part of these eigenvalues is due to the scattering term and is therefore to $\,$ rst approximation linear in

. The lifetime therefore diverges as 1= but for a nite value of we regard Eq. (69) as an approximation to the transport function and we will refer to this approach as the small scattering approximation.

In spite of the limited validity of the small scattering approximation it is useful in the sense that it is computationally much simpler to evaluate the transport function in the small scattering approximation than in the general

case. Therefore it can be used in order to obtain a rough idea of the behavior of the transport param eters.

The equations of the small scattering approximation are very similar to the formulae that have been used by other groups to compute the transport parameters of real materials 35,36,37 . In particular the assumption of constant lifetime is quite often used in practice, especially when the thermopower is being calculated. In this case we obtain

$$^{xx}() = ^{xx}();$$
 (71)

where the so called transport density, , is de ned as

$$^{xx}() = \frac{1}{V_C} {}_{k,p}^{x} (v_{k,p}^{x})^2 (+ F_{k,p}^{0});$$
 (72)

Num erical tests have shown that while the small scattering approximation can be quite good for broad bands it does not work well in narrow bands such as the dynamically generated quasiparticle bands of strongly correlated systems due to constant time approximation used.

In the case of the therm opower we obtain

$$S = \frac{k_{B}}{\dot{p}\dot{p}\dot{p}} \frac{R_{1}}{R_{1}} \frac{xx()f()f()f()()}{xx()f()f()}$$

$$T = \frac{10}{\dot{p}\dot{p}} \frac{k_{B}}{\dot{p}\dot{p}} \frac{2k_{B}T}{3} \frac{d}{d} \ln xx() : (73)$$

This of course is the classical M ott relation for the therm opower. In the literature this equation is often quoted with the transport density replaced by the spectral density and much emphasis placed on the fact that in case the Ferm i-level coincides with a Van H ove singularity the them opower diverges. This conclusion is not supported when the correct form for the therm opower is used since no Van H ove singularities are present in the transport density.

For free electrons the transport density is given by

$$^{xx}() = \frac{1}{12^2} \frac{2m_e}{h^2} = ^{3=2};$$
 (74)

and therefore we get

$$S = \frac{k_B}{\dot{F}} \frac{^2 k_B T}{2} \frac{1}{F} = n^{2=3} T \quad 0.281 \frac{nV}{K}; \quad (75)$$

where the density, n, is measured in electrons per cubic Bohr radius and the temperature, T, is measured in Kelvin. In case the electrons is enhanced the thermopower will simply increase by the enhancement factor.

The enhancement of the therm opower can also be deduced from the Mott equation in case the only e ect of the real part of the self-energy is to change the e ective mass of the bands that cross the Ferm i-surface. If we assume that the change in elective mass is the same for

all the bands that participate in the transport the low-tem perature therm opower becomes

S'
$$\frac{k_B}{jej} \frac{^2k_B T}{3Z} \frac{d}{d} \ln ^{0;xx} ();$$
 (76)

where the non-interacting transport density $^{0;xx}$ () is dened by

$$^{0;xx}() = \frac{1}{V_C} {}_{k;p}^{X} (v_{k;p}^{0;x})^2 (+ E_{k;p}^{0});$$
 (77)

Here Z denotes the quasiparticle residue of the bands involved. Hence we see indeed that the low-tem perature therm opower is enhanced by a factor of $1=\!\!\mathrm{Z}$ compared to the non-interacting therm opower.

To sum m arize theoretical part of the paper we provide the computational scheme used to obtain the transport properties

ie.

run LDA program to obtain the Kohn-Sham (LDA) Hamiltonian

m ake tight-binding calculations (or downfolding) to extract kinetic part of the e ective H am iltonian

construct the Hubbard-like e ective Ham iltonian adding the Coulomb repulsion to the kinetic part of the ective Ham iltonian

run DMFT-QMC (SUNCA) solver to obtain the self-energy for the e ective H am iltonian

construct LDA+DMFT Ham iltonian upfolding the self-energy to the LDA Ham iltonian $\,$

run transport program with the LDA+DMFT Hamiltonian.

V. TEST SYSTEM AND DM FT RESULTS

A. Test System

To test obtained transport equations on a realistic system we decided to use doped LaTiO $_3$ compound. The La1 $_{\rm X}$ SrxTiO $_3$ series has been studied very extensively in the past 38,39,40,41,42,43 and can be regarded as being one of the prime examples exhibiting the Motthubard metal-insulator transition. The end compound LaTiO $_3$ when prepared well is a Motthubard insulator although in the literature it is often characterized as a correlated or a poor metal. At high temperature this material is paramagnetic. The other end compound SrTiO $_3$ is an uncorrelated band insulator with a direct gap of 3.3 eV. Electronic structure properties of the

 $\text{La}_1 \text{ }_{x}\text{Sr}_{x}\text{T iO}_3$ series is governed by the triple degenerate cubic t_{2g} bands of the 3d orbitals (d¹ ionic con guration)44. In the distorted structure of LaT iO 3 the degeneracy of the band has been lifted and the single electron occupies a very narrow, non-degenerate $d_{x\,v}$ band 45 . Studies of the magnetic susceptibility do indeed indicate that the electronic structure of the P bnm phase is that of a narrow dxy band, which then with doping changes into a broad t_{2q} band (calculated bandwidth is W = 2:7 eV) with degenerate $d_{x\,y}$, $d_{x\,z}$ and $d_{y\,z}$ orbitals in the Ibm m and Pm 3m phases. As a function of doping the material behaves as a canonical doped M ott insulator. The speci c heat and the susceptibility are enhanced, the Hall num ber is unrenorm alized while the photoem ission spectral function has a resonance with a weight that decreases as one approaches half lling. Very near half lling, (for dopings less than 8%) the physics is fairly complicated. At small doping an antiferrom agnetic metallic phase is observed 42,46,47.

To obtain LDA band structure of LaTiO $_3$ we used the liner mun-tin orbitals (LMTO) method in its atom ic sphere approximation (ASA) with the basis Ti(4s;4p;3d), O (2s;2p) and La(6s;5p;5d) assuming for simplicity instead a real orthorhombic structure with a small distortions a cubic one with the same volume and the lattice constant $a_0=7.40~a.u.$ This approximation brings to a slight overestimation of the elective bandwidth and underestimation of the band gap between valence and conduction bands. In photoem ission studies of LaTiO $_3^{12}$ similar basis has been used.

U sing LDA band structure one can com pute and com pare with experiment the linear coe cient of speci cheat which is simply given in terms of the density of states at the Ferm i level by

= 2:357
$$\frac{\text{m J}}{\text{m olK}^2}$$
 $\frac{\text{tot (E}_f) [\text{states/ (eV unitcell)}]}{\text{Z}}$; (78)

where Z is the quasiparticle residue or the inverse of the mass renormalization. In LDA calculations the value of Z is equal to one. Doping dependence of the linear coefcient of speci cheat in LDA calculations was computed within the rigid band model. Our results along with the experimental data are presented in Table I.

In general, we see that the LDA data for are lower than the experimental values, indicating a strong mass renormalization. We note also that as we get closer to the Mott-Hubbard transition the elective mass grows signicantly. What is consistent with DMFT modeling of the Mott-Hubbard transition which shows that indeed the elective mass diverges at the transition. We should note however that this is not a necessary signature for the Mott-Hubbard transition: in V_2O_3 the pressure driven metal-insulator transition is accompanied by the divergence of the elective mass whereas the doping driven transition in the same system does not show that divergence⁴⁹.

The physical picture of the studied material is quite

Doping	Experim ent	LDA
5%	16.52	3.23
10%	11.51	3.16
20%	8.57	3.00
30%	7.70	2.82
40%	6.21	2.67
50%	5.38	2.52
60%	4.55	2.38
70%	4.35	2.19
80%	3.52	2.10

TABLE I: The linear coe cient of specic heat, , for La_{1 x} Sr_x T iO $_3$ m easured in units of $\frac{m}{m}\frac{J}{\text{olk}^2}$. The experimental data is taken from 48 . LDA data for the linear coe cient of specic heat are computed from LaT iO $_3$ LDA DOS.

transparent, very near half lling (dopings less than 8%) the Fermi energy becomes very small and now is comparable with the exchange interactions and structural distortion energies. A treatment beyond single site DMFT then becomes important to treat the spin degrees of freedom . On the other hand for moderate and large doping, the K ondo energy is the dom inant energy and DMFT is expected to be accurate. This was substantiated by a series of papers which compared DMFT calculations in a single band or multiband Hubbard models using sim plied density of states with the physical properties of real m aterials. Ref. 50 addressed the enhancem ent of the m agnetic susceptibility and the specic heat as half lling is approached. The optical conductivity and the suppression of the charge degrees of freedom as the Mott insulator is approached was described in Refs. 51,52, the observation that the Hall coe cient is not renormalized was found in Refs. 53,54. Finally the therm oelectric power on model level using iterative perturbation theory (IPT) as impurity solver was investigated by Palsson et al. 55.

Given the fact that only very simple tight-binding param eterizations were used in those works, and the fact that a large number of experiments were twith the same value of parameters one should regard the qualitative agreement with experiment as very satisfactory. The photoem ission spectroscopy of this compound, as well as in other transition metal compounds are not completely consistent with the bulk data, and it has been argued that disorder, and modeling of the special surface environment is required to improve the agreement with experiment 56 . In this situation, it is clear that this is the simplest system for study, and it was in fact the 1st system studied by LDA+DMFT 3 .

The important questions to be addressed are the degree of quantitative accuracy of DMFT. Furtherm ore, given the simplicity of this system, and the existence of well controlled experiments, it is an ideal system for testing the e ects of dierent approximations within the LDA+DMFT scheme.

B. The model

As we pointed out in Sec. II for a correct description of a system with strong electron correlations one needs to bring the self-energy into the heavy orbitals. For this purpose a model which correctly describes the physics of interacting orbitals is needed. In this paper we consider a three-band H ubbard model which underlying non-interacting dispersion relation is that of the degenerate cubic t_{2g} band of the transition metal 3d orbitals. For simplicity the H ubbard interaction term is taken to be SU (6) invariant i.e. there is equal interaction between two electrons of opposite spin in the same orbital as there is between two electrons in dierent orbitals on the same e site. The more general case will be revisited in future publications.

Value of the interaction strength in our model is chosen large enough to exhibit metal-insulator behavior in the studied compound. In units of half bandwidth, D, the interaction strength is taken to be equal U = 5D. The interaction strength should be regarded as an input param eter which value has be adjusted to the experimental situation. Saying this, we mean the chosen interaction strengths should be good enough to reproduce as many physical properties as only possible with maximum proxim ity to experim ent. To investigate dependence of calculated physical properties on the interaction strength we calculate all properties studied in this paper for two values of C oulom b repulsion U = 3D and $5D \cdot O$ n the m odel level U = 4D is the value very close to the minimum interaction to get m etal-insulator transition (M II) for integer lling n = 1 even in three-fold degenerate Hubbard m odelusing D M FT as an instrum entwhich takes care of the interaction in the system. Hence our choice of the interaction should quarantee exploration of two physically di erent behaviours of the system with and without the M II . In literature absolute value of C oulom b interaction is magnitude under discussion mainly because there is no direct and reliable method to extract it neither experim entally no theoretically. The uncertainty between di erent theoreticalm ethods 12,57 attempted to estimate value of U is quite substantial ranging the interaction strength from 32 eV to 5 eV.

It should be noticed that although this choice of param eters is consistent with insulating behavior of this system it might have limited validity in the real system at low doping. Since La₁ $_{\rm x} \rm Sr_{\rm x} T$ iO $_3$ is known to undergo several structural transform ations upon doping and in particular the structure of LaT iO $_3$ is distorted away from the cubic perovskite structure and in fact the distortion lifts the degeneracy of the t_{2g} orbitals and the groundstate orbital is a narrow non-degenerate d_{xy} orbital. Hence one might expect that the M ott-Hubbard transition in this system would be better described in a one-band model (x < 0.08). At larger dopings (x > 0.08) it is how ever clear that the system is degenerate and thus our model can be expected to give a reasonably good description in the larger doping range. In the present paper

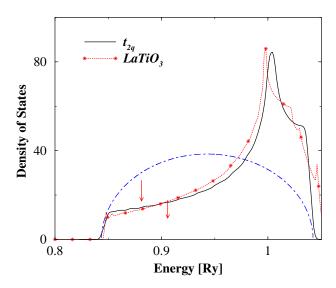


FIG. 7: LDA DOS of LaTiO $_3$ (dotted line with star symbols), its tight-binding t(solid line) and semicircular DOS (dotdashed line). A rrows indicate Fermi level position for lling n = 0.8 (the rst one is for the semicircular DOS, and the second one is for the tight-binding t).

we do not consider the e ect of lifting the degeneracy due to Jahn-Teller distortion rather we explore the tree-fold degenerate H ubbard m odel in the whole region of doping interval including n=1 point.

The kinetic part of the model Hamiltonian has been obtained from tight-binding LM TO ASA calculations. The band structure of the compound around the Ferm i level consists of three-fold degenerate Ti 3d t2g band, hosting one-electron, which is a rather well separated from an empty Ti3d eq band located above t2g band. A rather broad gap below t_{2g} separates Ti 3d and com pletely lled 2p oxygen band. Hence it is quite straight forward to make the tight-binding toft2g band to be used in in the impurity solvers. To achieve asymmetry in tight-binding DOS one needs take into account the next nearest neighbors, so called, t⁰ term on T isublattice. The dispersion which we obtained from the t is the following: $k = 2t(\cos k_x + \cos k_y) + 2t^0 \cos(k_x + k_y) + 2t_2 \cos k_z$, where t = 0.02424, $t^0 = 0.006$, $t_2 = 0.00151$ in Ry units. $t_{2\alpha}$ part of LaT iO $_3$ DOS (dotted line) and its t (solid line) are presented in Fig. 7. We also added one m ore curve in Fig. 7 corresponding to sem icircular DOS which we will use for dierent kind of benchmarking of our approach.

M aking tight-binding tofTi3d t_{2g} bands in LaTi0 $_3$ we electively do downfolding of the whole H am iltonian (better to say the main part of the H am iltonian without Ti3d t_{2g} bands) of the compound onto three t_{2g} bands i.e. we incorporate information of the whole H am iltonian into part of it. In this case H $_{\rm eff}$ and O $_{\rm eff}$ are 3 3 m atrices. H $_{\rm hh}$ and O $_{\rm hh}$ are parts of the H am iltonian and the overlap matrix corresponding to t_{2g} block of the original H am iltonian. H $_{11}$ and O $_{11}$ are parts of the H am iltonian

and the overlap m atrices of the H am iltonian w ithout t_{2g} block.

Our results of downfolding are presented in Fig. 8. We plotted bands of the whole H am iltonian which correspond to Ti3d t_{2g} bands by solid lines (the upper line is double degenerate one) and bands obtained from Eq. (21) by dashed lines. We see that bandwidth of t_{2g} bands ob-

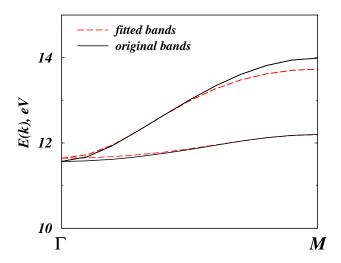


FIG. 8: t_{2g} bands of real band structure of LaTiO $_3$ (solid lines) and downfolded bands obtained from Eq. (21). The Ferm i level is at " $_{\rm F}$ = 12.54 eV .

tained from Eqs. (21) is only slightly smaller than the original one. The downfolding reproduces original band structure one-to-one in approxim ately 1 eV energy window around the chem ical potential. If one uses only H $_{\rm hh}$ and O $_{\rm hh}$ m atrices (not e ective H $_{\rm eff}$ and O $_{\rm eff}$ but sim – ply parts of the total H am iltonian corresponding to $t_{\rm 2g}$ block) one gets nearly dispersionless levels only as it is naturally expected.

As the last step in this section we calculate the transport function and the therm oelectrical power for three-fold degenerate tight-binding model. The transport function that we obtain for this model is shown in Fig. 9. We note that the slope of the transport function in the hole doping (< 0:0) regime is positive and therefore the LDA evaluation of the therm opower results in electron-like therm opower. The results for a few chosen doping values computed at temperature equal to 300 K are displayed in table II where we have also displayed the experimental results from Ref. 43.

It is quite noteworthy that for the two lowest doping values in the table the LDA and the experiment are in a good agreement. For higher values of doping however the experimental values are about twice as large as the LDA values. The good agreement at low doping should be regarded as mostly accidental one since the experimental data for doping values less than 5% show the hole-like thermopower which the LDA of course will not be able to reproduce.

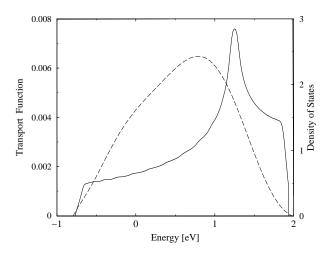


FIG. 9: The transport function for the LDA tight-binding Ham iltonian computed within the small scattering approximation with a constant lifetime for all orbitals along with DOS for n=0.8. Zero energy corresponds to the zero temperature Ferm i-level.

D oping	Experim ent	LDA data
5%	-52	- 5.6
25%	93	-7.8
50%	-18.3	-9.3
75%	-29.4	-18.2
80%	-41.2	-22.8

TABLE II: The therm opower, S, of La $_1$ xSr $_x$ TiO $_3$ at 300K m easured in units of V=K is computed using LDA band structure. The experim ental data are taken from 43 .

C. Sum mary of DM FT results

In the previous section we described how to obtain the Hubbard like Ham iltonian with kinetic part coming from downfolded bands and interaction part dened by renormalized Coulomb repulsion. In this section we address the issue how to compute and what is the main elect of the second part of the Ham iltonian, namely interactions, on physical properties of the studied system. Them ethod which we used to solve the Ham iltonian is the dynamical mean—eld theory which we described in section II.

Strong correlations dram atically renormalize tight-banding LDA DOS which we plot in Fig. 10 by dashed line. As it is seen from the plot it has bandwidth 2D and very asymmetric shape. In the same gure it is shown by solid line the renormalized DOS obtained from DMFT-QMC calculations at temperature $T=980~{\rm K}$. Instead one QP peak of the non-interacting $t_{\rm 2g}$ DOS we have nearly classical Hubbard DOS picture where the central peak of the non-renormalized DOS is redistributed between two Hubbard subbands and strongly renormalized central peak. Although the total bandwidth increases

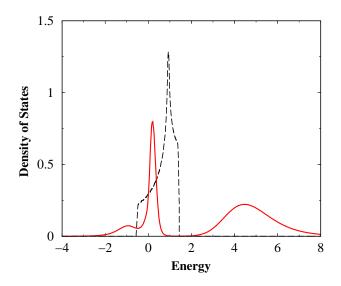


FIG. 10: Tight-binding (dashed lines) and renorm alized (solid line) D O Ses for lling n=0.8 and =32 at U=5D.

substantially, width of the central peak gets strongly reduced. We also notice the steepness of renormalized DOS at the chemical potential indicating reduction of the quasiparticle residue which is in LDA equal to one.

So, the main e ect expected from electron interactions is to reproduce the M ott transition when the system approaches an integer lling. One can see indications of the M IT in lling, n, dependencies of the chem ical potential, , and quasiparticle residue, Z . The M IT is clearly indicated by jump of versus n dependence (the chem ical potential changes while lling remains the same) plotted in Fig. 11 and also by vanishing energy scale seen in Z versus n dependence in Fig. 12 while approaching the M ott transition.

In Fig. 11 we plot the chem ical potential against lling around $\lim g = 1$ for three values of Coulomb interaction U = 3D; 4D and 5D in units of the half bandwidth and fortwo shapes of DOS (sem icircular and tightbinding). We notice here that both sem icircular and realistic D O S are renorm alized in such a way that they run in interval [D;D] with norm equal to one. First two upper curves presented in Fig. 11 correspond to U = 3D. The upper curve obtained using tight-binding DOS and lower one comes from semicircular DOS. The rst curve is nearly a straight line crossing n = 1 point while the line corresponding to sem icircular DOS is about to make a jump which is clearly presented in the behaviour of U = 4D line. The jum p becom es even m ore pronounced for U = 5D and both, sem icircular and tight-binding, DO Ses. Let us notice that absolute value of the jump for tight-binding DOS is smaller that for sem icircular DOS. From this gure one can easily conclude that the critical interaction when insulating behaviour appears in the system should be som ewhere between U = 3D and U = 4Dcloser to the second value (the nal conclusion about the insulating behaviour one can make from energy depen-

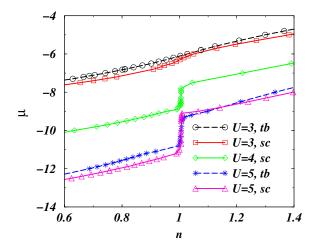


FIG. 11: The chem ical potential, , versus lling, n for sem icircular (sc) and tight-binding (tb) DOSes and various values of interaction, U, and temperature = 16.

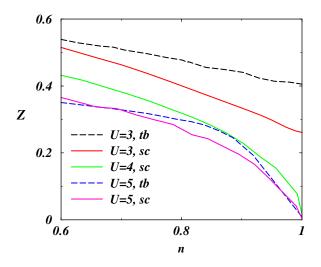


FIG. 12: Density dependence of the quasiparticle residue, Z, for sem icircular (sc) and tight-binding (tb) D O Ses and various values of interaction, U and temperature = 16.

dence of DOS on realaxis).

Similar to the against n dependence the M IT behaviour one can observe from the doping dependence of the quasiparticle residue which is presented in Fig. 12. In Fig. 12 we plot vecurves for the same values of interaction and shapes of DOSes as in the previous graph. As we expected for U = 3 (both DOSes) and n = 1 we have a nite value of Z. Notice that again (as in the previous plot) tight-binding DOS shows more metallic behaviour (larger value of Z and more straight line than in the case of semicircular DOS). All other values of the interaction clearly show insulating behaviour of the system.

So, now when one can see how electron correlations change physical behaviour of the system, we rem ind that the main input to DMFT-QMC or DMFT-SUNCA pro-

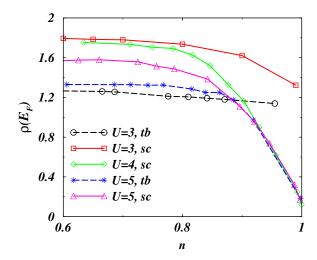


FIG.13:DOS at the Ferm i.level, (E $_{\rm F}$) [states=(eV unitcell)], vs lling,n,for sem icircular (sc) and tight-binding (tb)DOSes and various values of interaction, U. All of the data was computed for = 16.

cedure consists from the shape of DOS (sem icircle or tight-binding) and the value of interaction, U. We will analyze both shapes of DOSes for two values of U mentioned above.

U sing our results presented in Fig. 12 and behaviour of ($E_{\rm F}$) presented in Fig. 13 we can calculate the linear coe cient of speci c heat, . As we saw above, LDA results di er a lot from experimental values for . Now we want to know whether we can get any improvements applying DMFT, which changes the quasiparticle residue, Z, and renormalizes DOS.

In Fig. 14 we plot the linear coe cient of speci cheat against lling for di erent values of Coulomb repulsion and sem icircular and tight-binding DOSes. We can notice that for the same repulsion strength the linear coefcient of speci c heat for the sem icircular D O S is larger than fortight-binding DOS which follows from largerpinning value in the case of sem icircular DOS. Comparing U dependencies for the sem icircular D O Ses we see that the linear coe cient of speci cheat for U = 3D is nearly linear function till $\lim g = 1$ which one can explain by alm ost linear dependence of the quasiparticle residue. For U = 4D and U = 5D doping dependence of the linear coe cient of speci c heat reproduces the experim ental behaviour and the only question left is how close theoretical and experim ental results are. From the plot we see that in general results the sem icircular D O Ses are far from the experiment while for the tight-binding DOS the experim ental curve just in between U = 3D and U = 5Dlines. We can claim a rather good agreem ent (contrary to LDA situation) between DMFT and experim ental curves for whole range of dopings. The divergence of the linear coe cient of speci c heat shows the d-electron effective mass at the Fermilevel is strongly enhanced on approaching the M II 46 . In the case of U = 5D a small \overshooting" of the linear coe cient of speci c heat for large doping can be explained by $10\text{--}15\,\%$ inaccuracy in the procedure of the quasiparticle extraction (we dene it from the self-energy on M atsubara axis), plus one can slightly tune the interaction strength, which probably should be smaller something like 4.5 4.8D. In general agreement between DMFT-QMC results and experimental one is quite good.

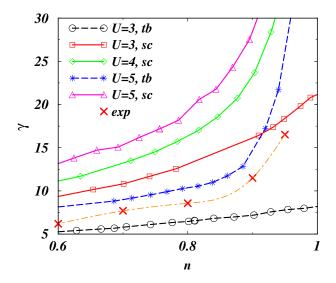


FIG .14: The linear coe cient of speci cheat, $[m J=m olK^2]$, vs. the density for di erent interaction strength and D O Ses at temperature = 16.

So we can sum marize the linear coe cient of speci c heat results saying that changes in the spectral weight, Z, are the main source of the improvement of our results for the linear coe cient of the speci cheat. Those changes are most remarkable for U=5D where Z tends to zero while density approaches the integer lling n=1. Diverging behaviour of linear coe cient of speci cheat for small doping in the real material can be explained by one of the structural transitions happening in LaTiO 3, at doping less than 5% the three-fold degeneracy is lifted and we electively have only one-band model for which U=3D could be large enough to get the M IT transition at integer lling.

Besides the degeneracy and the structural transition, tem perature belongs to major players on the eld of the M IT . The energy scale which separates low and high tem peratures is given by D 0 = ZD where D is uncorrelated bandwidth of the system and Z is the quasiparticle residue. Since the metal-insulator transition is accompanied by the vanishing of the quasiparticle residue we see that in order to access the low-tem perature phase we need to go to lower and lower tem peratures as we get closer to integer lling. Hence we can not expect to be able to see clear evidence of the divergence of for the range of tem peratures we are working in QMC approaching integer lling.

D. Comparison QMC and SUNCA

In this section we analyze and compare two impurity solversie. QMC and SUNCA which have been described in section III. Below we present results of those two m ethods and choose one of them to compute transport. Similar to the case of LDA calculation, in calculation the im purity problem we also need to make a compromise between speed and accuracy. It is wellknown that QMC im purity solver is very expensive but exact (the only approxim ation used in QMC is the Trotter break up) while SUNCA is cheap method but it is based on more approxim ations. QMC works in imaginary time and Matsubara frequency domain while SUNCA works on real frequency axis. To com pute transport properties one needs the selfenergy on real axis. In the case of QMC it is necessary to make the analytical continuation using maximum entropy or singular decom position m ethod to get the selfenergy on real axis as it was described in section IIIC. This is the weakest point in the DM FT-QMC procedure. DMFT-SUNCA working on real axis has the self-energy im m ediately after the self-consistency is reached.

A swe noticed in the previous subsection the main task of the interaction (read the inpurity solver) is to produce the M IT at integer llings. And one of the criteria of insulating behaviour in the system is vanishing quasiparticle weight. In Fig. 15 we compare the quasiparticle residue, Z obtained from DMFT-QMC and DMFT-SUNCA methods as function of doping for U=5D and realistic DOS. We see that both methods are in a good agreement with each other. We also provide Z versus neurve calculated using iterative perturbative theory 58 (PT) to see that all three in purity solvers produce at least qualitatively the same trends.

Now we can go further and compare electron GF on Matsubara axis. Imaginary axis is a natural space of work for QMC and to compare results with SUNCA we used Lehmann representation connecting spectral function on realaxis with GF on imaginary axis. The representation is analytical and exact, hence, the comparison can be made without any assumptions and approximations or uncertainties which could arise in the case of the analytical continuation.

In Fig. 16 we plot real and im aginary parts of GF on M atsubara axis for QMC (symbols) and SUNCA (lines) at di erent dopings and tem perature = 2 where one would expect very good agreement for the methods (as higher tem perature as better and faster both methods work). And indeed it is the case for all the curves. In Fig. 17 we plot GF and imaginary parts of the self-energy for lower tem perature, = 16 (tem perature which is mostly used in our calculations) and for 10 and 20% of dopings (they are our usual dopings used in calculations).

As we can conclude from presented curves we have quite good agreement between the two methods and hence we can use SUNCA in our transport calculations where behaviour of the self-energy on real axis around

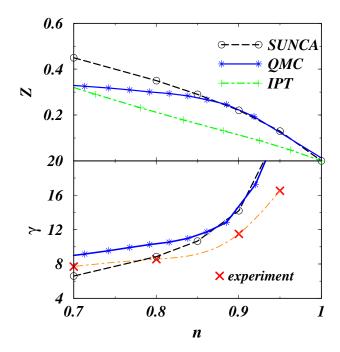


FIG. 15: Filling dependence of the quasiparticle residue, Z, and the linear coe cient of specicheat, , obtained from two impurity solvers: QMC (solid line with stars) and SUNCA (dashed line with circle symbols) for U = 5D, temperature = 16. Experimental points are given by cross symbols and dot-dashed line is used as a guide for eye. Tight-binding density of states was used in the self-consistency loop of the DMFT procedure. For comparison we also provide Z vs n curve obtained with IPT method for the same parameters as ones used in OMC and SUNCA calculations.

the Ferm i level is very crucial for the transport properties which are extremely sensitive to the shape, slope and value of the self-energy at the Ferm i level. Transport properties become more and more sensitive to all the details of the transport function at the Ferm i energy with lowering temperature. Taking into account all the comparisons made and calculations done we conclude that SUNCA is fast and accurate enough method in comparison with QMC to compute the transport properties of the compound.

VI. RESULTS OF TRANSPORT CALCULATIONS

A . Spectral and transport functions in the real $$\operatorname{\sc system}$$

Before to do transport computations it is worth to study spectral and transport functions dependencies on doping and temperature. As we discussed in the previous section VD we will use SUNCA as main method to compute transport properties (one can avoid the analytical continuation procedure in this case). But, at any rate,

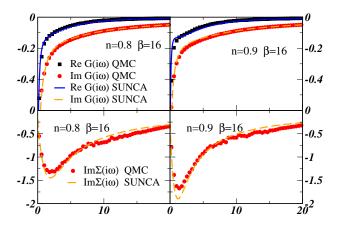


FIG. 16: Comparison of energy dependencies of imaginary and real parts of GF on Matsubara axis for dierent dopings computed using two impurity solvers: QMC (circles) and SUNCA (solid line) used in DMFT self-consistency procedure with semicircular DOS for U=5D and temperature =2.

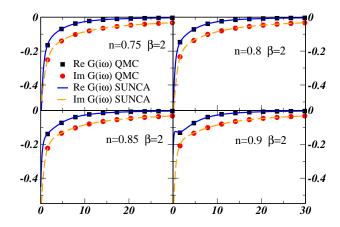


FIG.17: In the two upper panels we compare energy dependencies of imaginary and real parts of GF on M atsubara axis for dopings n = 0.8 and 0.9 computed using QMC (circles) and SUNCA (solid line). In the low panels we plot imaginary parts of the self-energies for the same parameters as in the upper panels. We used semicircular DOS in DMFT self-consistency procedure and U = 5D at temperature = 16.

we also did calculations with QMC impurity solver and compare results obtained from the two impurity solvers and describe di erences between them when they are the most noticeable.

In Fig. 18 we plotted the density of states per spin (the lower Hubbard band and quasiparticle peak are shown in the main panel and the inset shows the whole energy range) at lling n = 0.8 for various values of temperature. Here temperature is measured in units of the half-bandwidth, D = 1.35 eV and thus the actual temperature range is quite large with the smallest temperature, corresponding to T = 0.05D, being around 780 K. The highest temperature plotted is equal to one but it is still not large enough to make incoherent motion in the system to be dominant. As we can see temperature changes are quite

substantial (the lower H ubbard band nearly disappeared and quasiparticle peak is shifted towards the upper H ubbard band, indicating tendency to join the upper H ubbard band and form incoherent broad bum p) but they are still not enough to reach the incoherent m otion state (the upper H ubbard band is changed but still it is very good separated from the QP peak { lower H ubbard band creation). This situation is the expected one as we know the QP picture disappears for temperature higher then C oulom b repulsion, U, which is 5D in our case. Hence, for T 5D one will see only incoherent motion in the system. Let us notice here the dierence between SUNCA and QMC where in the last method the spectral density is just a single hum p corresponding to purely incoherent carrier dynam ics observed already for temperature

= 1. If we start from incoherent picture and low-ering tem perature, then the incoherent hump splits up and the Hubbard bands start to form. For even lower tem perature the lower Hubbard band moves completely below the Ferm i-surface and the coherent quasiparticle peak appears at the Ferm i-level. The lower Hubbard band starts to form at = 4,QP peak is formed for

10. For tem perature lower then $\,=\,16$ weight of the QP peak nearly does not change. We observe similar behaviour of DOS in SUNCA where the shape of the QP and the lower Hubbard band change only slightly for tem peratures lower then T = 0:1D . Described discrepancies on real axis between the two methods are entirely in the domain of the analytical continuation which is maximum entropy method which reliably reproduces only lowenergy part. One more interesting thing we should notice in Fig. 18 which is temperature dependence of DOS value at the Fermilevel. When this value reaches the one of non-interacting DOS we say that the pinning condition is obeyed. The temperature when the pinning condition is reached is called the pinning temperature and it strongly depends on doping. For lling n = 0:8 as we can conclude

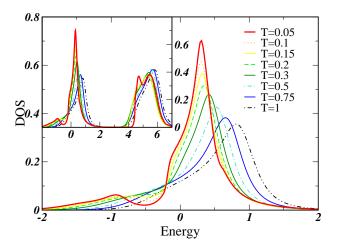


FIG .18: Tem perature dependence of DMFT density of states for n = 0.8 and U = 5D . Larger frequency interval is plotted in the insert. Energy is in units of half bandwidth, D .

In Fig. 19 we plotted the density of states per spin for T = 0.05 and dierent values of doping. Choice of tem perature was dictated by consideration that it should be lower than the pinning tem perature for the largest lling presented. With doping growing the quasiparticle peak broadens and its spectral weight increases a lot while the weight of the lower Hubbard band changes a little (doping changes are 10-20%). All the weight, which the QP peak gained, came from the upper Hubbard band (see insert in Fig. 19 where larger energy interval is presented). With doping increasing the system becomes less and less correlated and in the lim it of 100% doping Hubbard bands vanish and the quasiparticle peak transforms into free and empty tight-binding band. With doping decreasing the QP peak vanishes and the system becomes insulating for the repulsion $U = 5D \cdot Aswem entioned it before, for$ three-band degenerate Hubbard model, U = 3D, which is often used in description of LaT iO 3, is not enough to reproduce the insulating behaviour. which appears only 4:5 5D.

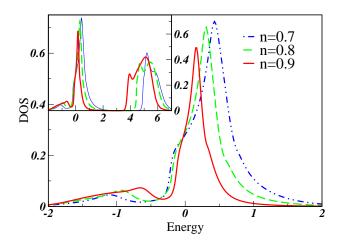


FIG. 19: Doping dependence of DMFT density of states for T=0.05 and U=5D. Larger frequency interval is plotted in the insert. Energy is in units of half bandwidth, D.

In Figs. 20 and 21 we presented dependence of im aginary part (main panels) and real part (inserts) of the self-energy on tem perature and doping for the sam e tem peratures as in Figs. 20 and the same dopings as in Fig. 21. In Fig. 20 we see nice quadratic behavior of the self-energy for low temperatures with the minimum at around the chem ical potential (zero in our case) which is then rises and shifts with the temperature to the right-hand side. Real part of the self-energy re ects the quasiparticle residue, Z, and with lowering the tem perature the QP residue increases and approaches the pinning value. The doping dependence of the imaginary part of the self-energy shows that the self-energy at the chem ical potential decreases with increasing of doping. This is exactly what one should expect for a system close to free-electron state where more quadratic and smaller im aginary part of the self-energy is anticipated. The real part of the self-energy shows the same tendency with increasing doping as in the case of the tem perature dependence: the curve which crosses the Ferm i level becomes more at. At zero doping it should have zero derivative at the chemical potential signaling about Z=1. The self-energy is extremely important characteristic of the system as it the only quantity which enters into transport calculations. Using the self-energy one computes the transport functions which is main ingredient of all transport equations.

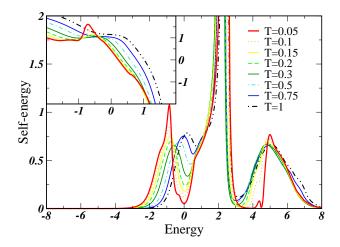


FIG. 20: Tem perature dependence of im aginary part of the self-energy for n=0.8. In the inset realpart of the self-energy is shown for the same tem peratures. Energy is in units of half bandwidth, D.

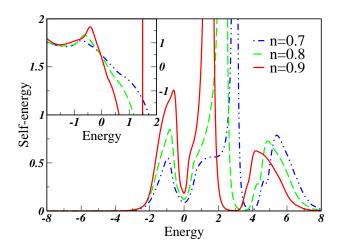


FIG. 21: Doping dependence of im aginary part of the self-energy for T=0.1. In the inset real part of the self-energy is shown for the same dopings. Energy is in units of half bandwidth, D.

In Figs. 22 and 23 we plot temperature and density dependencies of the transport function for the same set of parameters as we used for Figs. 20 and 21, correspondingly. One can reveal similar features as in density of states: in the transport function behaviour one clearly identies contributions coming from the upper Hubbard

band and lower one plus the Q P peak. But the most important contribution to transport properties at low temperatures comes from energy region around the Fermi level. As it can be seen from Eqs. (55) the transport coe cients are entirely dened by the transport function integral in an energy window which depends on temperature. These equations allow at least qualitatively to dene at least sign of the therm opower for small temperatures. If the slope of transport function is uprising then the therm opower should be negative and for the other slope it should be positive. For large energy window the sign of the therm opower will strongly depend on shape and position to the chemical potential of the transport function.

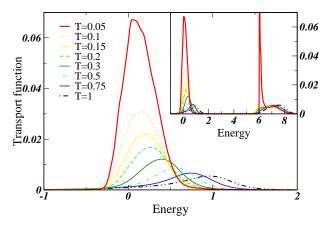


FIG. 22: Tem perature dependence of the transport function for n=0.8. In the inset larger frequency interval is used. Energy is in units of half bandwidth, D.

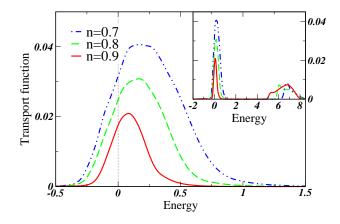


FIG. 23: Doping dependence of the transport function for temperature T=0.1. In the inset larger frequency interval is shown. Energy is in units of halfbandwidth, D.

B. Transport param eters

In Fig. 24 we plotted the transport parameters of the studied system for dierent densities against tempera-

ture. The transport param eters under consideration are the following: denotes the electrical resistivity, the therm al conductivity, S is the therm opower and L is the Lorentz ratio. The resistivity behaviour, as it was found experim entally 48 and theoretically, is a quadratic function at relatively low-tem perature interval becoming linear at higher tem peratures (see Fig. 25). The quadratic tem perature dependence of the electrical resistivity is rem in iscent of the strong electron-electron scattering which predom inate the electron (phonon scattering process. The thermal conductivity behaves as T 2 till tem peratures of order 10^3 10^4 , which are relatively large tem peratures 55. The Lorentz number tends to constant value around 16-17 nW = K 2 indicating the character of the low-tem perature scattering as Ferm i-liquid one. The therm opowerbehaviour is little bit more complicated. At low tem perature the therm opower linearly tends to zero. It is very hard for us to distinguish doping dependence for relatively small temperatures as all changes lay between error bars which are in our case larger than the di erence between lower and higher therm opower curves presented in the gure. The reason for large errors lays in a very small value of imaginary part of the self-energy which we have to deal with low ering the tem perature and this situation is very challenging for the used impurity solvers. For higher tem peratures (higher than 1000 K) we are curtain in the therm opower behaviour as there is no any problems with the self-energy determination in this tem perature range. With increasing tem perature we observe a localmaximum in the temperature interval 10^{3} 2 104. We associate it with increasing the tem perature cut-o (see Eq. (55)) which is large enough to take into account right-hand side slope of the central part in the transport function. Or in another words the localmaximum in the therm opower in some way mimics behaviour of the transport function (the hump around the chemical potential).

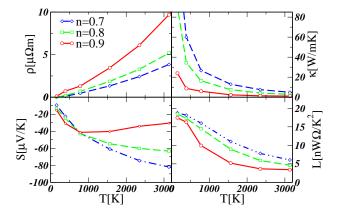


FIG. 24: Tem perature and doping dependencies of transport param eters: denotes the electrical resistivity, is the therm al conductivity, S is the therm opower and L is the Lorentz ratio.

A nalyzing Figs. 24 and 25 as functions of doping for a xed temperature we can see that all curves behave in the

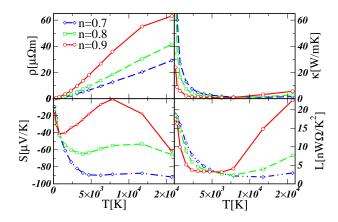


FIG. 25: The same transport parameters the same as in Fig. 24 but on substantially larger temperature interval.

way one would expect. The resistivity is growing with decreasing doping as the system approaches the M II while the therm alconductivity and the Lorentz number are decreasing. The therm opower has a bit more complicated behaviour which depends on xed temperature (which tem perature slice we take). But generally it is growing with vanishing doping and for lower than 10% doping one could get even positive them opower which rst becomes positive at temperatures around 5000 K (see n = 0.9them opower curve) and then positiveness will propagate to smaller temperatures. Comparing our results with experim ental situation in doped LaT iO 3 43,59 we notice that majority of experiments are done for temperature less than 300 K which is a rather hard task to deal with for the reason we pointed out above. The biggest discrepancy we found for resistivity at small temperatures where our resistivity 3-4 times lower than the experimental one. W hile the therm opower behaviour (which we also treat as electronic one) is accurate within 30 % in absolute value. One would expect that the therm opower could become positive with decreasing doping in the way it is experimentally observed. We also could obtain it once we do a much more delicate and hard job taking into account the structural transition happening at doping x < 0.05as e ectively we should have one-band model instead of three-fold degenerate. But this is beyond of the scope of the present work. C lose to the M II we have strongly asymmetric DOS and transport functions which in the case of integer $\lim n = 1$ will produce positive sign of the them opower. The reason for this is the position of negative slope (right-hand side) of the lower Hubbard band with is closer to the Ferm i energy than the upper one and hence has dom inant contribution into the transport properties of the system.

So, it would be fair to say that our calculations we can catch at least sem i-qualitative behaviour of the transport param eters. The electrical resistivity would require an additional treatm ent to get quantitatively a good agreement while the therm opower calculations deserve quantitative comparison with experiment and can be accurate

enough providing 20-30 % agreem ent with experim ent.

VII. CONCLUSION

In the paper we proposed and implemented a new method for calculation of them oelectrical properties in real materials. Dynamical mean-eld theory was used to take into account strong electron interactions and thereby bring the self-energy into rst-principal calculations. Taking a rather generic for many strongly correlated materials density of states, we obtained temperature and doping dependencies for such them oelectric properties as electrical resistivity, the thermal conductivity, the therm opower and the Lorentz ratio.

We believe that the new method will be a powerful tool for the analysis of existing experimental data and guiding us to a proper physical understanding of them oelectrical phenomena. This is especially important not only for correlated materials such as Mott-Hubbard insulators and high-tem perature superconductors but also for simple materials like the noble metals which display them oelectric behavior that still lacks a proper description. In addition we hope this new method will aid in the search for new materials with better them oelectrical performance by allowing for ab initio predictions of them oelectric properties.

A cknow ledgm ents

We would like to thank A. Lichtenstein form any fruit-ful and stimulation discussions. We greatly acknow ledge usage of Cray T3E-900 computer at NERSC, Berkeley, as well as Rutgers Beowulf computational cluster which allowed us to make present computations feasible.

APPENDIX A:MANY BODY THEORY IN A NON-ORTHOGONAL BASIS

Our starting point here is a representation of the kinetic term of the Hamiltonian in an orthogonal basis, fjiig and we assume that this basis is related to the non-orthogonal basis, fj ig by the transformation matrix

$$jii = X$$
 j iS i and $hij = X$ h j S i $= X$ $S_i^+ h j$: (A.1)

The Hamiltonian is now given by

The last term in the equation above is a requirem ent that $w \in p$ lace on the creation and destruction operators in the

non-orthogonal basis and thus we nd that

$$c^{+} = {\overset{X}{c_{i}^{+}}} S_{i}^{+}$$
 and $c = {\overset{X}{s_{j}^{-}}} S_{j} c_{j}$: (A 3)

The non-orthogonality of the basis is encoded in the overlap m atrix, O = h j i and this m atrix can be related to the transform ation m atrix, S in the following m anner

$$_{ij} = hijji =$$
 $S_{i}^{+} h j iS_{j} =$
 $S_{i}^{+} O S_{j}$
(A 4

Therefore we see that the overlap matrix is given by

$$O = (SS^+)^{-1}$$
: (A 5)

W e should note here that the creation operator c^+ does not create a particle in the state j i when acting on the vacuum , since as we see

$$c^{+} \mathcal{D}i = \begin{array}{ccc} X & & & X \\ c_{i}^{+} S_{i}^{+} \mathcal{D}i = & \mathbf{j}iiS_{i}^{+} & & & \\ & X^{i} & & \dot{X} & & \dot{X} \\ & & \dot{\mathbf{j}} & iS_{i}S_{i}^{+} = & \dot{\mathbf{j}} & iO^{-1}; \end{array}$$

$$(A 6)$$

It is how ever worth noting that this state has unit overlap with the state j i and zero overlap with all of the other basis-states! The commutation relationship of these operators are the same as for regular Ferm ioperators except that we get

$$fc^{+}$$
; $cg = X$
 $S_{j}fc_{i}^{+}$; $c_{j}gS_{i}^{+} = S_{i}S_{i}^{+} = 0^{-1}$: (A7)

Let us nally obtain the expression for the G reen's function in the non-orthogonal basis

G () =
$$hc$$
 () c^{\dagger} (0)i: (A8)

The easiest way to calculate this G reen's function is by looking at the Lagrangian for the system in the orthogonal basis and then simply transform it into the non-orthogonal one. We have (sum mation over repeated indices implied)

$$L = c_{i}^{+} \frac{\theta}{\theta} c_{i} \quad c_{i}^{+} H_{ij} c_{j}$$

$$= S_{i}^{-1} c^{+} \frac{\theta}{\theta} c \quad (S^{+})_{i}^{-1} \quad c^{+} H \quad c$$

$$= c^{+} O \quad \frac{\theta}{\theta} c \quad c^{+} H \quad c : \qquad (A 9)$$

The free M atsubara G reen's function can now be obtained by Fourier transform ing the operators in the Lagrangian and then the inverse of the G reen's function, G 0 (i!), is simply the term multiplying $c^\dagger\,c$. Thus we obtain

$$G^{0}$$
 (!) = [i!O H] ¹: (A 10)

The renormalized Green's function one gets as in the orthogonal case by adding the self-energy to the Hamiltonian and thus

$$G(i!) = [i!O H]$$
: (A11)

W e should rem ark here that these G reen's functions do not share the sam e properties as their cousins in the orthogonal bases do and in particular the total density is not given by trace of G (= 0). To see that we go back to the orthogonal basis where we know how things work and write the density operator as

Thus the total density of electrons in the system is

$$n_{tot} = h i = {\overset{X}{}} 0 \quad hc^{+} c i = {\overset{X}{}} G \quad (=0)0$$
 : (A13)

We should note in particular that this means that there seems to be no good way of assigning a density to a particular orbital in the non-orthogonal case.

APPENDIX B:LDA HAM ILTONIAN IN NON-ORTHOGONAL BASE

In LDA one has to solve the known K ohn-Sham equation

$$(r^2 + V)_{kj} = k_{jkj}$$
 (B1)

The eigenfunctions $_{\rm k\,j}$ are expanded in a basis set for example the LM TO basis $_{\rm k}$ (r) which is not necessary orthogonal as

$$_{kj} = {}^{X}$$
 A_{kj} $_{k}$: (B2)

Substituting (B2) in (B1) we obtain

$$H_{LDA}(k)A_{kj} = k_jO_k A_{kj};$$

with the normalization condition

$$X$$
 $A_{kj}O_{k} A_{kj^{0}} = j_{j^{0}}$:

The density of states w ith a particular character ; is de ned as

$$'$$
 () = $X_{kj} O_k A_{kj} (kj)$: (B3)

The DOS of the tight-binding t one can get from Eq. (B3) restricting index j to the three bands near the Ferm i level. Fig. 7 displays the partial $t_{\rm 2g}$ DOS

of LaTiO $_3$ (Eq. (B3) with of t_{2g} character). The total DOS one can get from Eq. (B3) sum ming over indexes

$$() = X \\ ()_{kj} (B4)$$

Notice that the eigenvectors A_{kj} are the matrix elements $(S_{kj} = A_{kj})$ of the Cholesky decomposition of 0 1 dened in Appendix A and that the partial DOS is normalized to be of one integrated over the whole frequency range. Held et al. 13 proposed to use the partial t_{2g} DOS, the low-frequency range with a recalling so as to normalize it to one

$$n_{t_{2g}} = X$$
 $n_{t_{2g}} = (")f("):$
(B 5)

APPENDIX C:SPLINES AND FOURIER TRANSFORMATIONS

1. Direct Fourier Transform ation

In QMC program we do the direct Fourier transform ation exactly, i.e. rst we obtain coe cients of the cubic spline exploiting physical properties of GF transformed and then make analytical Fourier integration knowing the form of the splined curve. The cubic spline interpolation formula reads

G() =
$$a_i + b_i$$
(i) + c_i (i)² + d_i (i)³; 2 [i ; $i+1$];

where one cients $a_i;b_i;c_i;d_i$ are equal to values of the function, its rst, second and third derivatives at knot i i.e. $a_i = G(i); b_i = G^0(i); c_i = G^0(i); d_i = G^{00}(i)$:

Or in term s of GF values, $G_i = G(_i)$; and its second derivative, $M_i = G^{(0)}(_i)$, only

$$a_{i} = G_{i};$$

$$b_{i} = \frac{G_{i+1} G_{i}}{h} \frac{2M_{i} + M_{i+1}}{6}h;$$

$$c_{i} = \frac{M_{i}}{2};$$

$$d_{i} = \frac{M_{i+1} M_{i}}{6h}:$$
(C1)

From equations above we see that one needs to know the second derivatives, M $_{\rm i}$, using tabulated values of G F , G $_{\rm i}$, in order to get the cubic spline interpolation. To obtain M $_{\rm i}$ coe cients we use conditions of sm oothness of the rst derivative and continuity of the second one. A sthe result we have L + 1 equations for L + 3 unknowns

where L is a number of time slices. In addition to L + 1 M $_0$;::M $_n$, n=0;::L, unknowns d_0 and d_n also should be provided. Last two unknowns entirely depend on the boundary conditions which we have to specify in order to have a unique solution of Eq. (C2). If one knows the rst derivatives at the end-points then d_0 and d_n are dened through

$$_{0} = 1$$
; $d_{0} = \frac{6}{h} \cdot \frac{G_{1} \cdot G_{0}}{h} \cdot G_{0}^{0}$; $G_{0} = 1$; $d_{n} = \frac{6}{h} \cdot G_{n}^{0} \cdot \frac{G_{n} \cdot G_{n-1}}{h}$;

and $d_i = \frac{3}{h} \quad \frac{G_{\,i+\,1} \quad G_{\,i}}{h} \quad \frac{G_{\,i-\,G_{\,i-\,1}}}{h}$; $_i = _{-i} = \frac{1}{2}$; for i 2 [1;n 1]:M ore detailed derivations of the above form ulae one can nd in Ref. 60.

W e can reduce number of unknowns just putting M $_{\rm 0}$ and M $_{\rm n}$ to zero (it is so called natural spline boundary conditions). In this case

$$_{0} = 0; d_{0} = 0; _{n} = 0; d_{n} = 0;$$

and we have the number of unknownsm atching the number of equations, L + 1.

This boundary condition is good enough to compute FT of GF in the system at or close to half lling since the second derivative of the G reen's function is small in absolute value in this regime. And using the natural spline boundary condition we do not im pose a noticeable error. However, away from half lling when the asymmetry of the system grows, along with amplitude, of one out of the two second derivatives, usage of the natural spline eventually leads to pathological behavior of the self-energy. The signature of this pathology is in the \overshooting" e ect 61 when the self-energy at som e nite M atsubara frequency i.e. the imaginary part of the self-energy, becom espositive in som e frequency region on the positive M atsubara half-axis while it should be always negative. This, of course, amounts to having negative spectral weight for the self-energy which is something that does not occur for ferm ionic response functions. The \overshooting" can get especially severe in the limiting cases of small temperatures, small particle densities or large interaction strength.

So, to avoid the problem with the self-energy and, hence, with the whole procedure of the self-consistency in DMFT-QMC program we need to use the proper boundary conditions. And in this case we have two possibilities to get unique solution for the system of Eq. (C2) exploiting physical properties of studied GF:a) we can provide the rst derivatives at both ends separately (in the next section we show how to calculate those derivatives) or b) we can provide the sum of the rst and the sum of the second derivatives at the end-points, so called the rst and the second m oments of GF.

W ith the second choice of the boundary conditions (b) the system of equations become three-diagonal one with

two o -diagonal elements in the opposite corners of the matrix (M $_{\rm n-1}$ and $-\frac{1}{2}$ M $_{\rm 0})$

where
$$d_0 = \frac{6}{h} \frac{G_1 G_0}{h} + \frac{G_n G_{n-1}}{h} M^{(1)} + 2M^{(2)}$$
, $d_{n-1} = \frac{6}{h} \frac{G_n + G_{n-2} 2G_{n-1}}{h} \frac{1}{2}B$, $G_0^0 + G_n^0 = M^{(1)}$, $M_0 + M_n = M^{(2)}$.

Now having the second derivatives M $_i$ and, hence coe cients a $_i$; b_i ; c_i ; d_i we can take Fourier integral analytically

Sum G_m (!n) overm

$$G(!_n) = X^L G_m(!_n);$$

will give us the Fourier integral in frequency space.

2. Inverse Fourier transform ation

As it is well known G reen's function G (!) falls o as 1=! when ! ! 1 . In the program we deal with nite number of frequency points and cutting o 1=! tail one would make a rather crude approximation as the discontinuity of GF G () (imaginary time domain!) has been removed. In such situation, the high-frequency tail has to be extracted from GF G (!) and Fourier transformed analytically using the following Fourier relation

$$\frac{1}{i!_n}$$
 \$ [()+ n()]e; (C5)

where n() 1=[expf g] and = 1 depending on whether ! n is bosonic or ferm ionic.

The inverse Fourier transform ation for GF without the tail is made by straightforward sum mation over Matsubara frequencies. Once it has been done we add the information about the tail using Eq. (C 5).

APPENDIX D:MOMENTS

M om ents, M $^{(k)}$, are nothing else as the expansion of GF in frequency domain

G (!) =
$$\frac{X^{N}}{!} \frac{M^{(k)}}{!^{k+1}}$$
: (D1)

A nother de nition of k-degree m om ent is the following

$$M^{(k)} = d! !^k (!);$$
 (D2)

where (!) is density of states (DOS).

Moments M (k) can be bind to sum of GFs and sum of its derivatives in imaginary-time space as

$$(1)^{k+1} (G^{(k)} (0^+) + G^{(k)} (1)) = M^{(k)};$$
 (D3)

where k = 0; ::: N.

To show this one needs to take Fourier integral in parts

$$G (i!_n) = e^{i!_n} G ()d (D 4)$$

$$= \frac{X^N}{k=0} \frac{(1)^{k+1} (G^{(k)} (0^+) + G^{(k)} ())}{(i!_n)^{k+1}}$$

$$+ \frac{(1)^{N+1}}{(i!_n)^{N+1}} e^{i!_n} \frac{e^{N+1} G ()}{e^{N+1}} d :$$

So, to solve the system of Eq. (C3) we need to adhere to the proper boundary conditions which are expressed through the various m om ents of the G reen's function. W hat we need nally it to provide the rst threem om ents $M^{(0)}; M^{(1)}; M^{(2)}$. The rst m om ent for G reen's function is equal to one, the second m om ent proportional to the chemical potential in the system and the third one is a little bit m ore complicated and contains a density-density correlator. To show that we start with the single in purity Anderson model which reads

where " = " + $\frac{1}{2}$ " $_{\rm 6}$ $_{\rm 0}$ U $_{\rm 0}$, the 1st three moments be obtained from the following commutators

$$M^{(k)} = fL^k f ; f^y q_+ ;$$

where LO = [0; H] denotes the commutator of operator O with the Hamiltonian, and f::g+ is the anticommutator. A fter som e algebra one nds the following expressions for the m om ents

$$M^{(0)} = f; f^{y} = 1; \qquad (D6)$$

$$M^{(1)} = [f; H]; f^{y} = H + X \quad U \circ (n \circ \frac{1}{2});$$

$$M^{(2)} = [f; H]; H]; f^{y} = [f; H]; H; f^{y}] = H^{2} + 2H \quad U \circ (n \circ \frac{1}{2}) + H^{2} + 2H \quad U \circ (n \circ \frac{1}{2}) + H^{2} + 2H \quad U \circ U \circ (n \circ \frac{1}{2}) + H^{2} + H^{$$

where $\stackrel{P}{V_k^2} = M_0^2$ (M $_0^1$) 2 , and the m om ents M $_0^i$ are de ned by Eq. (D2) with (!) = D(!), D(!) is noninteracting DOS.

Sum ming up similar terms in SU (N) approximation

$$M^{(1)} = " + (2N 1)Un;$$
 (D7)
 $M^{(2)} = "^2 + 2" (2N 1)Un +$ (D8)

$$M^{(2)} = "^2 + 2" (2N 1)Un + X U^2 [(2N 1)n + hnni] + V_k^2;$$

where n is lling per band and per spin, $n=\frac{1}{p^2N}$ n , and double occupancy is de ned as hnni= $\frac{1}{p^2N}$ n oi.

The second way to make the correct cubic spline as wementioned before in section C 1 is to provide the rst derivatives at both ends of imaginary time interval (the boundary conditions). To nd the rst derivatives at the ends one can use the following de nition of the rst derivatives of nite-tem perature GF

$$\frac{\theta}{\theta}$$
 T f () $f^{y}(0) = T [H; f] f^{y} = G^{0}(0^{+})$:

Using as the Hamiltonian H = H_{SIAM} we can easily obtain the derivatives at the ends

In obtained formulae (Eqs. (D6)-(D9)) we should know lling, n , for each band and spin as well as we should know density-density correlator in oi. The 11ing we can extract from GF itself. Calculation of the correlator in QMC highlights one of the advantages of the method: the correlator is provided by the QMC itself and one does not need to rely on any additional approximations to obtain it as e.g. in the case of multiband IP T m ethod⁶² where coherent potential approximation is used to get the correlator. At each time slice the densitydensity correlator is also computed from GF but in im aginary time domain where it is simply a product of two Green's functions in (; 0) space. We should note here that we compute the correlator along with other parameters in the system at each iteration step and once the selfconsistency is reached we have correctly obtained all the components and parameters in the system. And nally, with smallenough imaginary time step one can com pletely avoid the \overshooting" problem . Keeping in m ind the main \lim itation of Q M C procedure U = 2 < 1.

In the present computations we choose = 1=4 which is good enough for the range of parameters we use in the current paper.

APPENDIX E:SUNCA EQUATIONS

In this Appendix, we explicitly give the SUNCA equations for degenerate Anderson in purity model with N=2 bands considering uctuations between states with M=1, M= and M+1 electrons on the inpurity. Self-energies are analytically continued to real frequencies and projected onto the physical Q=1 subspace. W= rst dene the ladder vertex functions T_a , T_b with rungs of pseudoparticles a (with M+1 electrons) and b (with M=1 electrons), respectively, as shown diagram matically in Fig.4. These vertex functions, obey the following Bethe { Salpeter equations,

$$T_{a}(!;) = 1 + (N M) df()A_{c}^{0}()G_{f}()G_{a}(+ !)T_{a}(;);$$

$$T_{b}(!;) = 1 + M df()A_{c}^{0}()G_{f}()G_{b}(+ !)T_{b}(;);$$
(E1)

where f () is the Ferm i function and A_c^0 () = $\frac{1}{2}$ Im G_c^0 () is the bare conduction electron density of states. For concreteness, all propagators are to be understood as the retarded ones. The auxiliary particle self(energies (Fig. 3) are then given by,

In order to calculate the local electron spectral function A_d from the self-consistently determined G_a , G_b , G_f , it is convenient to de nemodi ed vertex functions as

$$S_a^R(!;) = 1 + (N M) df()A_c^0()RefG_f()T_a(;)gG_a(+ !);$$
 (E6)

$$S_a^{I}(!;) = (N M) df()A_c^{0}()Im fG_f()T_a(;)gG_a(+!);$$
 (E7)

$$S_b^R(!;) = 1 + M d f()A_c^0()RefG_f()T_b(;)gG_b(!);$$
 (£8)

$$S_{b}^{I}(!;) = M \quad df() A_{c}^{0}() \text{ Im } fG_{f}() T_{b}(;) gG_{b}() !)$$
: (E9)

The local spectral function then reads

Note that the exponential divergencies of the statistical factors appearing in Eq. (E10) are compensated by the threshold behavior of the corresponding auxiliary particle spectral functions A (!) = $\frac{1}{2}$ Im G (!), = a;b;f in the integrands. For the num erical treatm ent, these divergencies can be explicitly absorbed by formulating the self(consistency equations (A1) { (A10) in term softhe functions A (!) which are de ned via

$$A (!) = f(!) \tilde{A} (!);$$
 (E11)

and, hence, have no exponential divergence. We thus have, e.g., $\exp(!) A (!) = f(!) A^{\sim} (!)$.

APPENDIX F:TRANSPORT CALCULATIONS: CURRENTS DER IVATION

Below we derive the expressions for the currents in a general basis. This is done by extending the gaugetheoretic method developed in Ref. 63. In the nonorthogonal basis the action for the system can be expressed as follows

Here $\hat{\theta} = \frac{1}{2} (\hat{\theta} + \hat{\theta})$ denotes the anti-sym m etrized time derivative. The particle and heat currents can now be obtained by considering the invariance of the action under local phase transform ation and local translations in tim e respectively. In the orthogonal case one is lead to the following expression for the currents

$$\tilde{\jmath} = \frac{\text{@H } [\![K_p]\!]}{\text{@} [\![K_p]\!]} \quad \text{and} \quad \mathcal{Q} = \frac{\text{@H } [\![K_h]\!]}{\text{@} [\![K_p]\!]};$$

$$\text{(F 2)}$$

where \mathcal{X}_p and \mathcal{X}_h are gauge elds conjugate to the currents and H [Ap] and H [Ah] denote the gauged Hamiltonian, i.e. the H am iltonian with the replacements \tilde{k} !

 ${\rm \tilde{K}} \quad {\rm \tilde{A}_p} \ {\rm and} \ {\rm \tilde{K}} \ ! \quad {\rm \tilde{K}} + {\rm \tilde{A}_h} \ {\rm \tilde{G}} \quad {\rm respectively.} \ {\rm This} \ {\rm replace-}$ m ent is perform ed in both the kinetic and the interaction term s but not in the eld operators. In our case however the overlap matrix appearing in the action depends also on m om entum and therefore the proper generalization of the currents to non-orthogonal basis will also take the overlap m atrix into account. Thus we obtain

$$\gamma = \frac{0 (O [K_p] \stackrel{\$}{0} + H [K_p])}{0 K_p} \dot{j}_{k_p=0};$$
(F3)

$$Q = \frac{@ (O [X_h] \stackrel{\$}{@} + H [X_h])}{@ X_h} \dot{x}_{h=0}$$
: (F4)

Performing these operations leads to the following expressions

$$\gamma = X$$
 $v_k; B_k^{(0)} u_k; B_k^{(1)};$
(F5)

$$\mathcal{I} = \begin{bmatrix}
X \\
\Psi_{k}, & B_{k}^{(0)} \\
X
\end{bmatrix}$$

$$\mathcal{I} = \begin{bmatrix}
X \\
\Psi_{k}, & B_{k}^{(1)} \\
X
\end{bmatrix}$$

$$\mathcal{I} = \begin{bmatrix}
X \\
\Psi_{k}, & B_{k}^{(1)} \\
\Psi_{k}, & B_{k}^{(1)}
\end{bmatrix}$$

$$\mathcal{I} = \begin{bmatrix}
X \\
\Psi_{k}, & B_{k}^{(1)} \\
\Psi_{k}, & B_{k}^{(2)}
\end{bmatrix}$$

$$\mathcal{I} = \begin{bmatrix}
X \\
\Psi_{k}, & B_{k}^{(1)} \\
\Psi_{k}, & B_{k}^{(2)}
\end{bmatrix}$$

$$\mathcal{I} = \begin{bmatrix}
X \\
\Psi_{k}, & B_{k}^{(1)} \\
\Psi_{k}, & B_{k}^{(2)}
\end{bmatrix}$$

$$\mathcal{I} = \begin{bmatrix}
X \\
\Psi_{k}, & B_{k}^{(1)} \\
\Psi_{k}, & B_{k}^{(2)}
\end{bmatrix}$$

$$\mathcal{I} = \begin{bmatrix}
X \\
\Psi_{k}, & B_{k}^{(1)} \\
\Psi_{k}, & B_{k}^{(2)}
\end{bmatrix}$$

$$\mathcal{I} = \begin{bmatrix}
X \\
\Psi_{k}, & B_{k}^{(1)} \\
\Psi_{k}, & B_{k}^{(2)}
\end{bmatrix}$$

$$\mathcal{I} = \begin{bmatrix}
X \\
\Psi_{k}, & B_{k}^{(1)} \\
\Psi_{k}, & B_{k}^{(2)}
\end{bmatrix}$$

where we have de ned

$$B_{k;}^{(n)} = (1)^n c_{k;}^+ (0)^n c_{k;}^+$$
 (F7)

and

$$\nabla_{k}$$
; = $\frac{1}{h} \tilde{r}_k H_{k}^0$, and u_k ; = $\frac{1}{h} \tilde{r}_k O_k$; (F8)

where H_k^0 is the tight-binding, LM TO Ham iltonian of the system and 0_k ; is the overlap matrix that captures the non-orthogonality of the basis that we are using. The validity of the expressions above is not restricted to DMFT and they are in fact true for all density-density interactions such as the Hubbard interaction. This is because the interaction terms are gauge invariant and therefore they do not contribute to the expressions for the currents.

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